PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Family Datasheet

General Description

PSoC™ 4 is a scalable and reconfigurable platform architecture for a family of programmable embedded system controllers with an Arm® Cortex®-M0 CPU. It combines programmable and reconfigurable analog and digital blocks with flexible automatic routing. The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE product family, based on this platform, is a combination of a microcontroller with an integrated Bluetooth® Low Energy, also known as Bluetooth Smart, radio and subsystem (BLESS). The other features include digital programmable logic, high-performance analog-to-digital conversion (ADC), opamps with Comparator mode, and standard communication and timing peripherals. The programmable analog and digital subsystems allow flexibility and in-field tuning of the design.

Features

- 32-bit MCU Subsystem
  - 48-MHz Arm Cortex-M0 CPU with single-cycle multiply and DMA
  - Up to 256 KB of flash with Read Accelerator
  - Up to 32 KB of SRAM
- Bluetooth LE Radio and Subsystem
  - Bluetooth LE 4.2 support
  - 2.4-GHz RF transceiver with 50-Ω antenna drive
  - Digital PHY
  - Link-Layer engine supporting master and slave modes
  - RF output power: –18 dBm to +3 dBm
  - RX sensitivity: –89 dBm
  - RX current: 18.7 mA
  - TX current: 15.6 mA at 0 dBm
  - Received Signal Strength Indication (RSSI): 1-dB resolution
- Programmable Analog
  - Four opamps with reconfigurable high-drive external and high-bandwidth internal drive, Comparator modes, and ADC input buffering capability. Can operate in Deep Sleep mode.
  - 12-bit, 1-Msps SAR ADC with differential and single-ended modes; Channel Sequencer with signal averaging
  - Two current DACs (IDACs) for general-purpose or capacitive sensing applications on any pin
  - Two low-power comparators that operate in Deep Sleep mode
- Programmable Digital
  - Four programmable logic blocks called universal digital blocks, (UDBs), each with eight macrocells and data path
  - Infineon-provided peripheral component library, user-defined state machines, and Verilog input
- Power Management
  - Active mode: 1.7 mA at 3-MHz flash program execution
  - Deep Sleep mode: 1.5 µA with watch crystal oscillator (WCO) on
  - Hibernate mode: 150 nA with RAM retention
  - Stop mode: 60 nA
- Capacitive Sensing
  - Capacitive Sigma-Delta (CSD) provides best-in-class SNR (>5:1) and liquid tolerance
  - Infineon-supplied software component makes capacitive sensing design easy
  - Automatic hardware tuning algorithm (SmartSense™)

- Segment LCD Drive
  - LCD drive supported on all pins (common or segment)
  - Operates in Deep Sleep mode with four bits per pin memory
- Serial Communication
  - Two independent run-time reconfigurable serial communication blocks (SCBs) with reconfigurable I^2C, SPI, or UART functionality
- Timing and Pulse-Width Modulation
  - Four 16-bit timer/counter pulse-width modulator (TCPWM) blocks
  - Center-aligned, Edge, and Pseudo-random modes
  - Comparator-based triggering of Kill signals for motor drive and other high-reliability digital logic applications
- Up to 36 Programmable GPIOs
  - 7 mm × 7 mm 56-pin QFN package
  - 76-ball CSP package
  - 68-ball CSP package
  - Any GPIO pin can be CapSense, LCD, analog, or digital
  - Two overvoltage-tolerant (OVT) pins; drive modes, strengths, and slew rates are programmable
- PSoC Creator™ Design Environment
  - Integrated Design Environment (IDE) provides schematic design entry and build (with analog and digital automatic routing)
  - API components for all fixed-function and programmable peripherals
- Industry-Standard Tool Compatibility
  - After schematic entry, development can be done with Arm-based industry-standard development tools

More Information

There is a wealth of data at **http://www.cypress.com** to help you to select the right PSoC device for your design, and to help you to quickly and effectively integrate the device into your design. For a comprehensive list of resources, see the introduction page for **Bluetooth Low Energy Products**. Following is an abbreviated list for PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE:

- Overview: **PSoC Portfolio**, **PSoC Roadmap**
- Product Selectors: **PSoC 1**, **PSoC 3**, **PSoC 4**, **PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE**, **PSoC 5LP.** In addition, PSoC Creator includes a device selection tool.
- Application Notes: There are a large number of PSoC application notes coverting a broad range of topics, from basic to advanced level. Recommended application notes for getting started with PRoC-BLE with PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE
- are:
  - **AN91267**: Getting Started with PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE
  - **AN97060**: PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE and PRoC-BLE - Over-The-Air (OTA) Device Firmware Upgrade (DFU) Guide
  - **AN91184**: PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE - Designing Bluetooth LE Applications
  - **AN91162**: Creating a Bluetooth LE Custom Profile
  - **AN91445**: Antenna Design and RF Layout Guidelines
  - **AN96841**: Getting Started With EZ-BLE Module
  - **AN85951**: PSoC 4 CapSense Design Guide
  - **AN95089**: PSoC 4-/PRoC-BLE Crystal Oscillator Selection and Tuning Techniques
  - **AN92584**: Designing for Low Power and Estimating Battery Life for Bluetooth LE Applications
- Technical Reference Manual (TRM) is in two documents:
  - **Architecture TRM** details each PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE functional block
  - **Registers TRM** describes each of the PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE registers
- Development Kits:
  - **CY8CKIT-042-BLE-A** Pioneer Kit, is a flexible, Arduino-compatible, Bluetooth LE development kit for PRoC-BLE with PSoC™ 4 CY8C4xxx-BL MCU with AIROC™ Bluetooth® LE.
  - **CY8CKIT-142**, PSoC™ 4 with AIROC™ Bluetooth® LE Module, features a PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE device, two crystals for the antenna matching network, a PCB antenna and other passives, while providing access to all GPIOs of the device.
  - **CY8CKIT-143**, PSoC™ 4 with AIROC™ Bluetooth® LE 256KB Module, features a PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE 256KB device, two crystals for the antenna matching network, a PCB antenna and other passives, while providing access to all GPIOs of the device.
  - The **MiniProg3** device provides an interface for flash programming and debug.

PSoC Creator

PSoC Creator is a free Windows-based Integrated Design Environment (IDE). It enables concurrent hardware and firmware design of PSoC 3, PSoC 4, and PSoC 5LP based systems. Create designs using classic, familiar schematic capture supported by over 100 pre-verified, production-ready PSoC Components; see the **list of component datasheets**. With PSoC Creator, you can:

1. Drag and drop component icons to build your hardware system design in the main design workspace
2. Codesign your application firmware with the PSoC hardware, using the PSoC Creator IDE C compiler
3. Configure components using the configuration tools
4. Explore the library of 100+ components
5. Review component datasheets

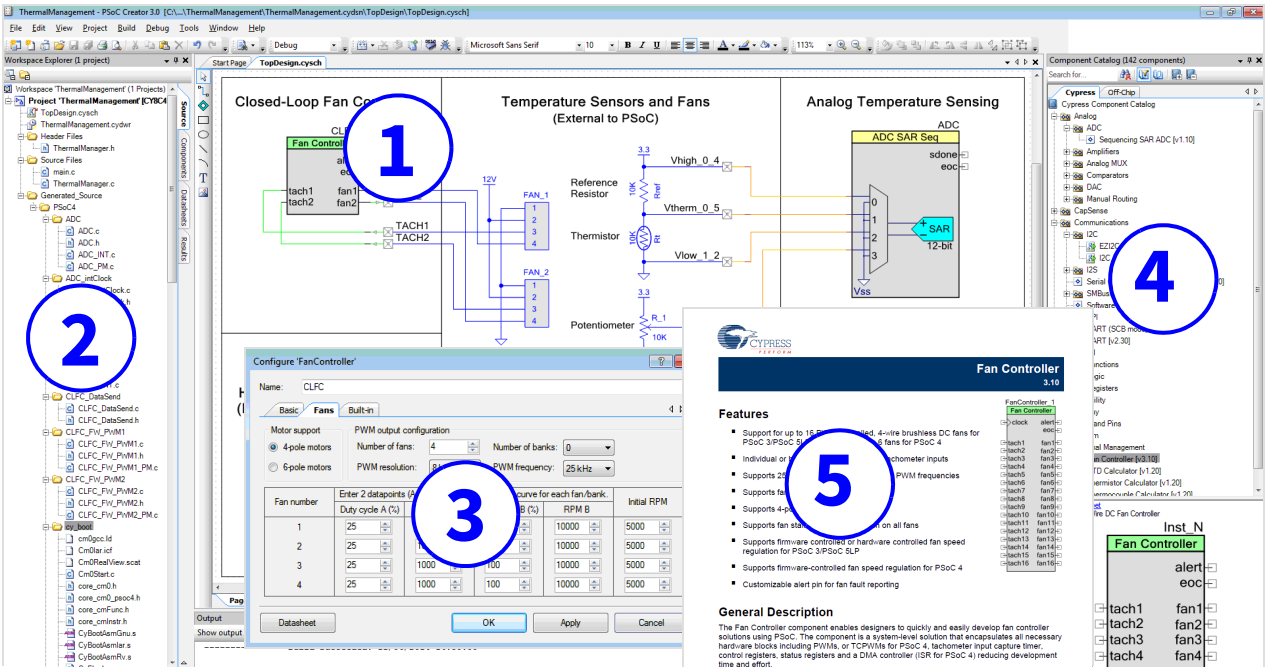


Figure 1. Multiple-Sensor Example Project in PSoC Creator Contents

Contents

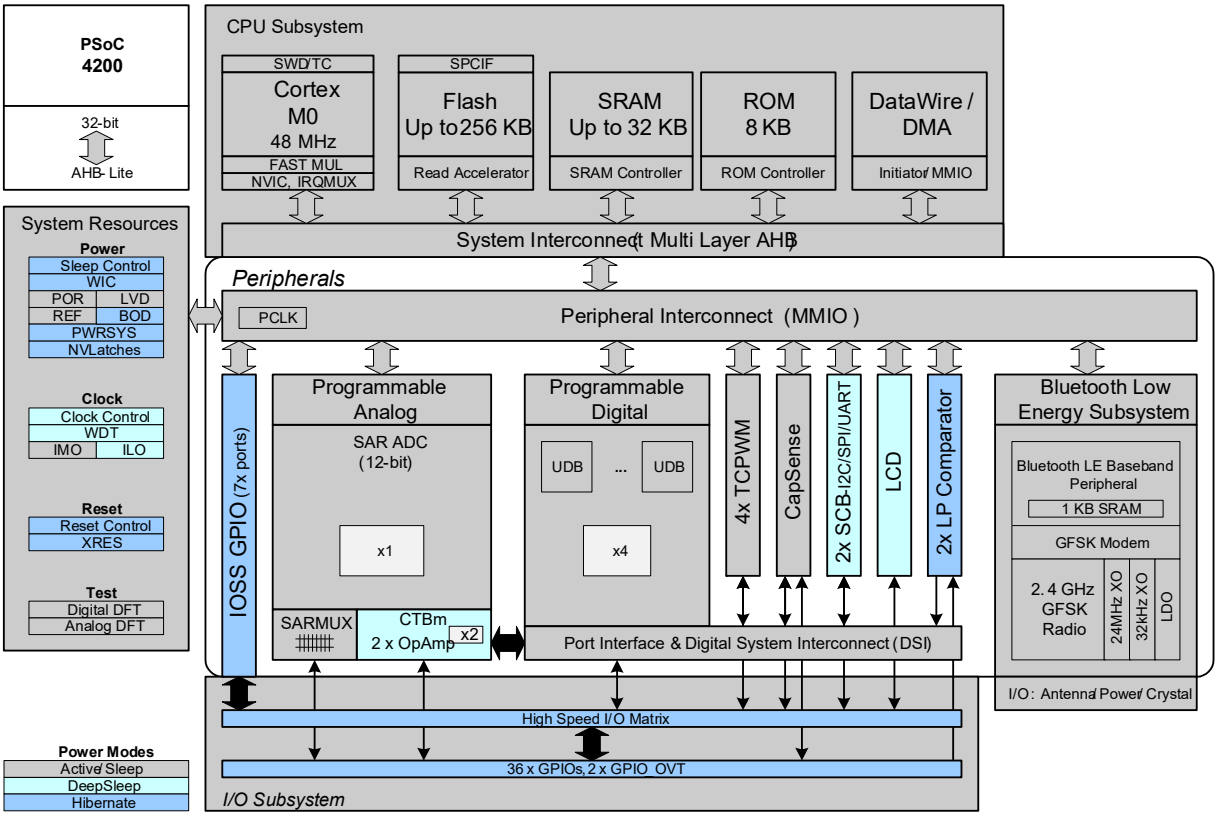


Figure 2Block Diagram

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The Arm SWD interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debugging.

The PSoC Creator IDE provides fully integrated programming and debugging support for the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE devices. The SWD interface is fully compatible with industry-standard third-party tools. With the ability to disable debug features, very robust flash protection, and allowing customer-proprietary functionality to be implemented in on-chip programmable blocks, the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE family provides a level of security not possible with multi-chip application solutions or with microcontrollers.

Debug circuits are enabled by default and can only be disabled in firmware. If not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with the new firmware that enables debugging.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. Because all programming, debug, and test interfaces are disabled when maximum device security is enabled, PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE with device security enabled may not be returned for failure analysis. This is a trade-off the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE allows the customer to make.

Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher-performance processors such as Cortex-M3 and M4. The implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and a wakeup interrupt controller (WIC). The WIC can wake the processor up from the Deep Sleep mode, allowing power to the main processor to be switched off when the chip is in the Deep Sleep mode. The Cortex-M0 CPU provides a nonmaskable interrupt (NMI) input, which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes an SWD interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE device has a flash module with 256 KB of flash memory, tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 2 wait-state (WS) access time at 48 MHz and with 1-WS access time at 24 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average. Part of the flash module can be used to emulate EEPROM operation if required. Maximum erase and program time is 20 ms per row (256 bytes). This also applies to the emulated EEPROM.

SRAM

SRAM memory is retained during Hibernate.

SROM

The 8-KB supervisory ROM contains a library of executable functions for flash programming. These functions are accessed through supervisory calls (SVC) and enable in-system programming of the flash memory.

DMA

A DMA engine, with eight channels, is provided that can do 32-bit transfers and has chainable ping-pong descriptors.

System Resources

Power System

The power system is described in detail in the section **Power on page 24**. It provides an assurance that the voltage levels are as required for the respective modes, and can either delay the mode entry (on power-on reset (POR), for example) until voltage levels are as required or generate resets (brownout detect (BOD)) or interrupts when the power supply reaches a particular programmable level between 1.8 and 4.5 V (low voltage detect (LVD)). PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE operates with a single external supply (1.71 to 5.5 V without radio, and 1.9 V to 5.5 V with radio). The device has five different power modes; transitions between these modes are managed by the power system. PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes. Refer to the *Technical Reference Manual* for more details.

Clock System

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no metastable conditions occur.

The clock system for PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE consists of the internal main oscillator (IMO), the internal low-speed oscillator (ILO), the 24-MHz external crystal oscillator (ECO) and the 32-kHz watch crystal oscillator (WCO). In addition, an external clock may be supplied from a pin.

IMO Clock Source

The IMO is the primary source of internal clocking in PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 to 48 MHz in steps of 1 MHz. The IMO tolerance with Infineon-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low-power oscillator, which is primarily used to generate clocks for the peripheral operation in the Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. A software component is provided, which does the calibration.

External Crystal Oscillator (ECO)

The ECO is used as the active clock for the Bluetooth LE subsystem to meet the ±50-ppm clock accuracy of the Bluetooth 4.2 Specification. PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE includes a tunable load capacitor to tune the crystal clock frequency by measuring the actual clock frequency. The high-accuracy ECO clock can also be used as a system clock.

Watch Crystal Oscillator (WCO)

The WCO is used as the sleep clock for the Bluetooth LE subsystem to meet the ±500-ppm clock accuracy for the Bluetooth 4.2 Specification. The sleep clock provides an accurate sleep timing and enables wakeup at the specified advertisement and connection intervals. The WCO output can be used to realize the real-time clock (RTC) function in firmware.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO or from the WCO; this allows the watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register. With the WCO and firmware, an accurate real-time clock (within the bounds of the 32-kHz crystal accuracy) can be realized.

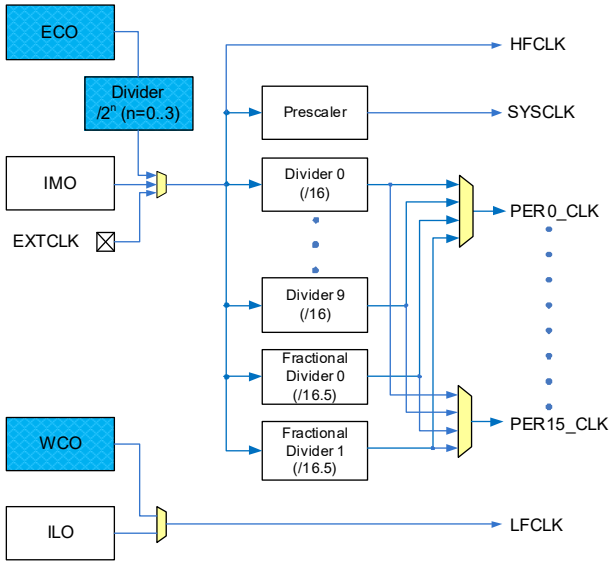


Figure 3 PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE MCU Clocking Architecture

The HFCLK signal can be divided down (see **Figure**) to generate synchronous clocks for the UDBs, and the analog and digital peripherals. There are a total of 12 clock dividers for PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE: ten with 16-bit divide capability and two with 16.5-bit divide capability. This allows the generation of 16 divided clock signals, which can be used by peripheral blocks. The analog clock leads the digital clocks to allow analog events to occur before the digital clock-related noise is generated. The 16-bit and 16.5-bit dividers allow a lot of flexibility in generating fine-grained frequency values and are fully supported in PSoC Creator.

Reset

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE device can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through resets and allows the software to determine the cause of the reset. An XRES pin is reserved for an external reset to avoid complications with the configuration and multiple pin functions during power-on or reconfiguration. The XRES pin has an internal pull-up resistor that is always enabled.

Voltage Reference

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE reference system generates all internally required references. A one-percent voltage reference spec is provided for the 12-bit ADC. To allow better signal-to-noise ratios (SNR) and better absolute accuracy, it is possible to bypass the internal reference using a REF pin or use an external reference for the SAR. Refer to **Table 19, “SAR ADC AC Specifications,”** on page 34 for details.

Bluetooth LE Radio and Subsystem

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE incorporates a Bluetooth Smart subsystem that contains the Physical Layer (PHY) and Link Layer (LL) engines with an embedded AES-128 security engine. The physical layer consists of the digital PHY and the RF transceiver that transmits and receives GFSK packets at 1 Mbps over a 2.4-GHz ISM band, which is compliant with Bluetooth Smart Bluetooth Specification 4.2. The baseband controller is a composite hardware and firmware implementation that supports both master and slave modes. Key protocol elements, such as HCI and link control, are implemented in firmware. Time-critical functional blocks, such as encryption, CRC, data whitening, and access code correlation, are implemented in hardware (in the LL engine).

The RF transceiver contains an integrated balun, which provides a single-ended RF port pin to drive a 50-Ω antenna via a matching/filtering network. In the receive direction, this block converts the RF signal from the antenna to a digital bit stream after performing GFSK demodulation. In the transmit direction, this block performs GFSK modulation and then converts a digital baseband signal to a radio frequency before transmitting it to air through the antenna.

The Bluetooth Smart Radio and Subsystem (BLESS) requires a 1.9-V minimum supply (the range varies from 1.9 V to 5.5 V).

Key features of BLESS are as follows:

- Master and slave single-mode protocol stack with logical link control and adaptation protocol (L2CAP), attribute (ATT), and security manager (SM) protocols
- API access to generic attribute profile (GATT), generic access profile (GAP), and L2CAP
- L2CAP connection-oriented channel
- GAP features
  - Broadcaster, Observer, Peripheral, and Central roles
  - Security mode 1: Level 1, 2, 3, and 4
  - Security mode 2: Level 1 and 2
  - User-defined advertising data
  - Multiple bond support
- GATT features
  - GATT client and server
  - Supports GATT sub-procedures
  - 32-bit universally unique identifier (UUID)
- Security Manager (SM)
  - Pairing methods: Just works, Passkey Entry, Out of Band and Numeric Comparison
  - Authenticated man-in-the-middle (MITM) protection and data signing
  - LE Secure Connections (Bluetooth 4.2 feature)
- Link Layer (LL)
  - Master and Slave roles
  - 128-bit AES engine
  - Encryption
  - Low-duty cycle advertising
  - LE Ping
  - LE Data Packet Length Extension (Bluetooth 4.2 feature)
  - Link Layer Privacy (with extended scanning filter policy, Bluetooth 4.2 feature)
- Supports all SIG-adopted Bluetooth LE profiles

Analog Blocks

12-bit SAR ADC

The 12-bit, 1-Msps SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The block functionality is augmented for the user by adding a reference buffer to it (trimmable to ±1%) and by providing the choice of three internal voltage references, V_{DD}, $V_{DD}/2$, and V_{REF} (nominally 1.024 V), as well as an external reference through a REF pin. The Sample-and-Hold (S/H) aperture is programmable; it allows the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. System performance will be 65 dB for true 12-bit precision provided appropriate references are used and system noise levels permit it. To improve the performance in noisy conditions, it is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through the selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, the aggregate sampling bandwidth is equal to 1 Msps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware-driven switching. A feature provided by the sequencer is the buffering of each channel to reduce CPU interrupt-service requirements. To accommodate signals with varying source impedances and frequencies, it is possible to have different sample times programmable for each channel. Also, the signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is able to digitize the output of the on-chip temperature sensor for calibration and other temperature-dependent functions. The SAR is not available in Deep Sleep and Hibernate modes as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 to 5.5 V.

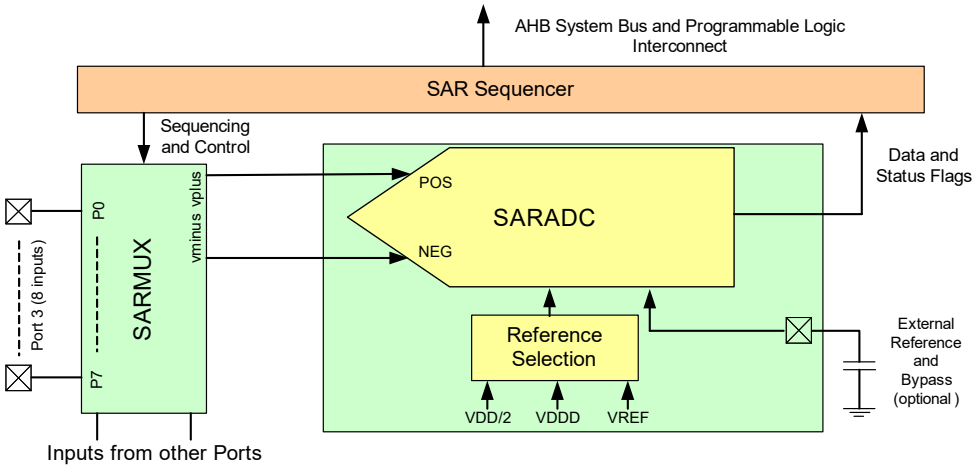


Figure 4SAR ADC System Diagram

Opamps (CTBm Block)

PSoC 42X8_BLE has four opamps with Comparator modes, which allow most common analog functions to be performed on-chip, eliminating external components. PGAs, voltage buffers, filters, transimpedance amplifiers, and other functions can be realized with external passives saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the sample-and-hold circuit of the ADC without requiring external buffering.

Temperature Sensor

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has an on-chip temperature sensor. This consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor is connected to the ADC, which digitizes the reading and produces a temperature value by using a Infineon-supplied software that includes calibration and linearization.

Low-Power Comparators

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has a pair of low-power comparators, which can also operate in Deep Sleep and Hibernate modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator-switch event.

Programmable Digital

Universal Digital Blocks (UDBs) and Port Interfaces

The PSoC 4XX8 BLE 4.2 has four UDBs; the UDB array also provides a switched Digital System Interconnect (DSI) fabric that allows signals from peripherals and ports to be routed to and through the UDBs for communication and control.

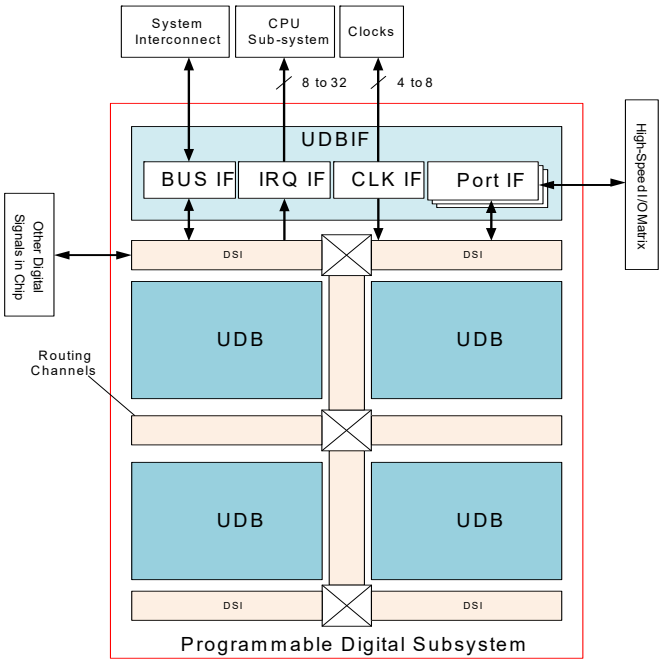


Figure 5UDB Array

UDBs can be clocked from a clock-divider block, from a port interface (required for peripherals such as SPI), and from the DSI network directly or after synchronization.

A port interface is defined, which acts as a register that can be clocked with the same source as the PLDs inside the UDB array. This allows a faster operation because the inputs and outputs can be registered at the port interface close to the I/O pins and at the edge of the array. The port interface registers can be clocked by one of

the I/Os from the same port. This allows interfaces such as SPI to operate at higher clock speeds by eliminating the delay for the port input to be routed over DSI and used to register other inputs (see **Figure**).

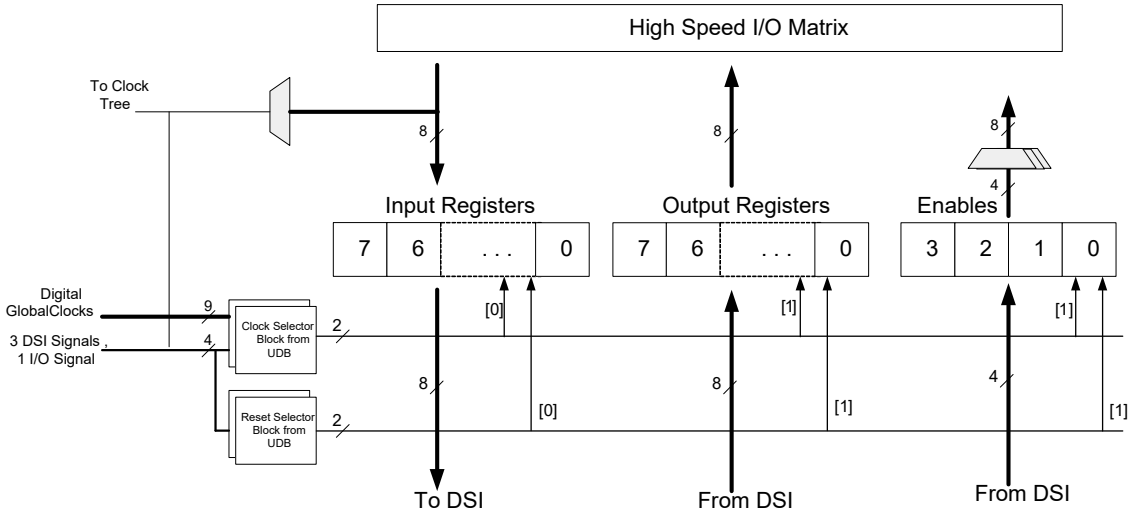


Figure 6. Port Interface

UDBs can generate interrupts (one UDB at a time) to the interrupt controller. UDBs retain the ability to connect to any pin on the chip through the DSI.

Fixed-Function Digital

Timer/Counter/PWM Block

The timer/counter/PWM block consists of four 16-bit counters with user-programmable period length. There is a Capture register to record the count value at the time of an event (which may be an I/O event), a period register which is used to either stop or auto-reload the counter when its count is equal to the period register, and compare registers to generate compare value signals which are used as PWM duty cycle outputs. The block also provides true and complementary outputs with programmable offset between them to allow the use as deadband programmable complementary PWM outputs. It also has a Kill input to force outputs to a predetermined state; for example, this is used in motor-drive systems when an overcurrent state is indicated and the PWMs driving the FETs need to be shut off immediately with no time for software intervention.

Serial Communication Blocks (SCB)

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has two SCBs, each of which can implement an I^2C, UART, or SPI interface.

I^2C Mode: The hardware I^2C block implements a full multi-master and slave interface (it is capable of multimaster arbitration). This block is capable of operating at speeds of up to 1 Mbps (Fast Mode Plus) and has flexible buffering options to reduce the interrupt overhead and latency for the CPU. It also supports EzI^2C that creates a mailbox address range in the memory of PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE and effectively reduces the I^2C communication to reading from and writing to an array in the memory. In addition, the block supports an 8-deep FIFO for receive and transmit, which, by increasing the time given for the CPU to read the data, greatly reduces the need for clock stretching caused by the CPU not having read the data on time. The FIFO mode is available in all channels and is very useful in the absence of DMA.

The I^2C peripheral is compatible with I^2C Standard-mode, Fast-mode, and Fast-Mode Plus devices as defined in the NXP I^2C-bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes.

SCB1 is fully compliant with Standard mode (100 kHz), Fast mode (400 kHz), and Fast-Mode Plus (1 MHz) I^2C signaling specifications when routed to GPIO pins P5[0] and P5[1], except for hot-swap capability during I^2C active communication. The remaining GPIOs do not meet the hot-swap specification (V_{DD} off; draw < 10-µA current) for Fast mode and Fast-Mode Plus, I_{OL} Spec (20 mA) for Fast-Mode Plus, hysteresis spec (0.05 V_{DD}) for Fast mode and Fast-Mode Plus, and minimum fall time spec for Fast mode and Fast-Mode Plus.

- GPIO cells, including P5.0 and P5.1, cannot be hot-swapped or powered up independent of the rest of the I^2C system.
- The GPIO pins P5.0 and P5.1 are over-voltage tolerant but cannot be hot-swapped or powered up independent of the rest of the I^2C system
- Fast-Mode Plus has an I_{OL} specification of 20 mA at a V_{OL} of 0.4 V. The GPIO cells can sink a maximum of 8 mA I_{OL} with a V_{OL} maximum of 0.6 V.
- Fast-mode and Fast-Mode Plus specify minimum Fall times, which are not met with the GPIO cell; the Slow-Strong mode can help meet this spec depending on the bus load.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows the addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated. Note that hardware handshaking is not supported. This is not commonly used and can be implemented with a UDB-based UART in the system, if required.

SPI Mode: The SPI mode supports full Motorola SPI, TI Secure Simple Pairing (SSP) (essentially adds a start pulse that is used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO for transmit and receive.

GPIO

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has 36 GPIOs. The GPIO block implements the following:

- Eight drive strength modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL)
- Pins 0 and 1 of Port 5 are overvoltage-tolerant pins
- Individual control of input and output buffer enabling/disabling in addition to drive-strength modes
- Hold mode for latching previous state (used for retaining the I/O state in Deep Sleep and Hibernate modes)
- Selectable slew rates for dV/dt-related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width. During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix (HSIOM) is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals are also fixed to reduce internal multiplexing complexity (these signals do not go through the DSI network). DSI signals are not affected by this and any pin may be routed to any UDB through the DSI network.

Data output and pin-state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE).

Special-Function Peripherals

LCD Segment Drive

PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE has an LCD controller, which can drive up to four commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as digital correlation and PWM.

The digital correlation method modulates the frequency and levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays.

The PWM method drives the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep mode, refreshing a small display buffer (four bits; one 32-bit register per port).

CapSense

CapSense is supported on all pins in PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE through a CapSense Sigma-Delta (CSD) block that can be connected to any pin through an analog mux bus that any GPIO pin can be connected to via an Analog switch. CapSense function can thus be provided on any pin or group of pins in a system under software control. A Component is provided for the CapSense block to make it easy for the user.

The shield voltage can be driven on another mux bus to provide liquid-tolerance capability. Liquid tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input.

The CapSense block has two IDACs which can be used for general purposes if CapSense is not being used (both IDACs are available in that case) or if CapSense is used without liquid tolerance (one IDAC is available).

Pinouts

Table 1 shows the pin list for the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE device. Port 3 consists of the high-speed analog inputs for the SAR mux. All pins support CSD CapSense and analog mux bus connections.

Table 1 PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Pin List (QFN Package)

Pin	Name	Type	Description
1	VDDD	POWER	1.71-V to 5.5-V digital supply
2	XTAL32O/P6.0	CLOCK	32.768-kHz crystal
3	XTAL32I/P6.1	CLOCK	32.768-kHz crystal or external clock input
4	XRES	RESET	Reset, active LOW
5	P4.0	GPIO	Port 4 Pin 0, lcd, csd
6	P4.1	GPIO	Port 4 Pin 1, lcd, csd
7	P5.0	GPIO	Port 5 Pin 0, lcd, csd
8	P5.1	GPIO	Port 5 Pin 1, lcd, csd
9	VSSD	GROUND	Digital ground
10	VDDR	POWER	1.9-V to 5.5-V radio supply
11	GANT1	GROUND	Antenna shielding ground
12	ANT	ANTENNA	Antenna pin
13	GANT2	GROUND	Antenna shielding ground
14	VDDR	POWER	1.9-V to 5.5-V radio supply
15	VDDR	POWER	1.9-V to 5.5-V radio supply
16	XTAL24I	CLOCK	24-MHz crystal or external clock input
17	XTAL24O	CLOCK	24-MHz crystal
18	VDDR	POWER	1.9-V to 5.5-V radio supply
19	P0.0	GPIO	Port 0 Pin 0, lcd, csd
20	P0.1	GPIO	Port 0 Pin 1, lcd, csd
21	P0.2	GPIO	Port 0 Pin 2, lcd, csd
22	P0.3	GPIO	Port 0 Pin 3, lcd, csd
23	VDDD	POWER	1.71-V to 5.5-V digital supply
24	P0.4	GPIO	Port 0 Pin 4, lcd, csd
25	P0.5	GPIO	Port 0 Pin 5, lcd, csd
26	P0.6	GPIO	Port 0 Pin 6, lcd, csd
27	P0.7	GPIO	Port 0 Pin 7, lcd, csd
28	P1.0	GPIO	Port 1 Pin 0, lcd, csd
29	P1.1	GPIO	Port 1 Pin 1, lcd, csd
30	P1.2	GPIO	Port 1 Pin 2, lcd, csd
31	P1.3	GPIO	Port 1 Pin 3, lcd, csd
32	P1.4	GPIO	Port 1 Pin 4, lcd, csd
33	P1.5	GPIO	Port 1 Pin 5, lcd, csd
34	P1.6	GPIO	Port 1 Pin 6, lcd, csd
35	P1.7	GPIO	Port 1 Pin 7, lcd, csd
36	VDDA	POWER	1.71-V to 5.5-V analog supply
37	P2.0	GPIO	Port 2 Pin 0, lcd, csd

Table 1 PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Pin List (QFN Package) *(continued)*

Pin	Name	Type	Description
38	P2.1	GPIO	Port 2 Pin 1, lcd, csd
39	P2.2	GPIO	Port 2 Pin 2, lcd, csd
40	P2.3	GPIO	Port 2 Pin 3, lcd, csd
41	P2.4	GPIO	Port 2 Pin 4, lcd, csd
42	P2.5	GPIO	Port 2 Pin 5, lcd, csd
43	P2.6	GPIO	Port 2 Pin 6, lcd, csd
44	P2.7	GPIO	Port 2 Pin 7, lcd, csd
45	VREF	REF	External reference input or bypass capacitor
46	VDDA	POWER	1.71-V to 5.5-V analog supply
47	P3.0	GPIO	Port 3 Pin 0, lcd, csd
48	P3.1	GPIO	Port 3 Pin 1, lcd, csd
49	P3.2	GPIO	Port 3 Pin 2, lcd, csd
50	P3.3	GPIO	Port 3 Pin 3, lcd, csd
51	P3.4	GPIO	Port 3 Pin 4, lcd, csd
52	P3.5	GPIO	Port 3 Pin 5, lcd, csd
53	P3.6	GPIO	Port 3 Pin 6, lcd, csd
54	P3.7	GPIO	Port 3 Pin 7, lcd, csd
55	VSSA	GROUND	Analog ground
56	VCCD	POWER	Regulated 1.8-V supply, connect to 1.3-µF capacitor.
57	EPAD	GROUND	Ground paddle for the QFN package

Table 2 PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Pin List (WLCSP Package)

Pin	Name	Type	Description
A1	NC	NC	Do not connect
A2	VREF	REF	External reference input or bypass capacitor
A3	VSSA	GROUND	Analog ground
A4	P3.3	GPIO	Port 3 Pin 3, analog/digital/lcd/csd
A5	P3.7	GPIO	Port 3 Pin 7, analog/digital/lcd/csd
A6	VSSD	GROUND	Digital ground
A7	VSSA	GROUND	Analog ground
A8	VCCD	POWER	Regulated 1.8-V supply, connect to 1-µF capacitor
A9	VDDD	POWER	1.71-V to 5.5-V digital supply
B1	NB	NO BALL	No Ball
B2	P2.3	GPIO	Port 2 Pin 3, analog/digital/lcd/csd
B3	VSSA	GROUND	Analog ground
B4	P2.7	GPIO	Port 2 Pin 7, analog/digital/lcd/csd
B5	P3.4	GPIO	Port 3 Pin 4, analog/digital/lcd/csd
B6	P3.5	GPIO	Port 3 Pin 5, analog/digital/lcd/csd
B7	P3.6	GPIO	Port 3 Pin 6, analog/digital/lcd/csd
B8	XTAL32I/P6.1	CLOCK	32.768-kHz crystal or external clock input
B9	XTAL32O/P6.0	CLOCK	32.768-kHz crystal
C1	NC	NC	Do not connect
C2	VSSA	GROUND	Analog ground
C3	P2.2	GPIO	Port 2 Pin 2, analog/digital/lcd/csd
C4	P2.6	GPIO	Port 2 Pin 6, analog/digital/lcd/csd
C5	P3.0	GPIO	Port 3 Pin 0, analog/digital/lcd/csd
C6	P3.1	GPIO	Port 3 Pin 1, analog/digital/lcd/csd
C7	P3.2	GPIO	Port 3 Pin 2, analog/digital/lcd/csd
C8	XRES	RESET	Reset, active LOW
C9	P4.0	GPIO	Port 4 Pin 0, analog/digital/lcd/csd
D1	NC	NC	Do not connect
D2	P1.7	GPIO	Port 1 Pin 7, analog/digital/lcd/csd
D3	VDDA	POWER	1.71-V to 5.5-V analog supply
D4	P2.0	GPIO	Port 2 Pin 0, analog/digital/lcd/csd
D5	P2.1	GPIO	Port 2 Pin 1, analog/digital/lcd/csd
D6	P2.5	GPIO	Port 2 Pin 5, analog/digital/lcd/csd
D7	VSSD	GROUND	Digital ground
D8	P4.1	GPIO	Port 4 Pin 1, analog/digital/lcd/csd
D9	P5.0	GPIO	Port 5 Pin 0, analog/digital/lcd/csd
E1	NC	NC	Do not connect
E2	P1.2	GPIO	Port 1 Pin 2, analog/digital/lcd/csd
E3	P1.3	GPIO	Port 1 Pin 3, analog/digital/lcd/csd
E4	P1.4	GPIO	Port 1 Pin 4, analog/digital/lcd/csd

Table 2 PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Pin List (WLCSP Package) *(continued)*

Pin	Name	Type	Description
E5	P1.5	GPIO	Port 1 Pin 5, analog/digital/lcd/csd
E6	P1.6	GPIO	Port 1 Pin 6, analog/digital/lcd/csd
E7	P2.4	GPIO	Port 2 Pin 4, analog/digital/lcd/csd
E8	P5.1	GPIO	Port 5 Pin 1, analog/digital/lcd/csd
E9	VSSD	GROUND	Digital ground
F1	NC	NC	Do not connect
F2	VSSD	GROUND	Digital ground
F3	P0.7	GPIO	Port 0 Pin 7, analog/digital/lcd/csd
F4	P0.3	GPIO	Port 0 Pin 3, analog/digital/lcd/csd
F5	P1.0	GPIO	Port 1 Pin 0, analog/digital/lcd/csd
F6	P1.1	GPIO	Port 1 Pin 1, analog/digital/lcd/csd
F7	VSSR	GROUND	Radio ground
F8	VSSR	GROUND	Radio ground
F9	VDDR	POWER	1.9-V to 5.5-V radio supply
G1	NC	NC	Do not connect
G2	P0.6	GPIO	Port 0 Pin 6, analog/digital/lcd/csd
G3	VDDD	POWER	1.71-V to 5.5-V digital supply
G4	P0.2	GPIO	Port 0 Pin 2, analog/digital/lcd/csd
G5	VSSD	GROUND	Digital ground
G6	VSSR	GROUND	Radio ground
G7	VSSR	GROUND	Radio ground
G8	GANT	GROUND	Antenna shielding ground
G9	VSSR	GROUND	Radio ground
H1	NC	NC	Do not connect
H2	P0.5	GPIO	Port 0 Pin 5, analog/digital/lcd/csd
H3	P0.1	GPIO	Port 0 Pin 1, analog/digital/lcd/csd
H4	XTAL24O	CLOCK	24-MHz crystal
H5	XTAL24I	CLOCK	24-MHz crystal or external clock input
H6	VSSR	GROUND	Radio ground
H7	VSSR	GROUND	Radio ground
H8	ANT	ANTENNA	Antenna pin
J1	NC	NC	Do not connect
J2	P0.4	GPIO	Port 0 Pin 4, analog/digital/lcd/csd
J3	P0.0	GPIO	Port 0 Pin 0, analog/digital/lcd/csd
J4	VDDR	POWER	1.9-V to 5.5-V radio supply
J7	VDDR	POWER	1.9-V to 5.5-V radio supply
J8	NO CONNECT	–	–

High-speed I/O matrix (HSIOM) is a group of high-speed switches that routes GPIOs to the resources inside the device. These resources include CapSense, TCPWMs, I^2C, SPI, UART, and LCD. HSIOM_PORT_SELx are 32-bit-wide registers that control the routing of GPIOs. Each register controls one port; four dedicated bits are assigned to each GPIO in the port. This provides up to 16 different options for GPIO routing as shown in **Table 3**.

Table 3 HSIOM Port Settings

Value	Description
0	Firmware-controlled GPIO
1	Output is firmware-controlled, but Output Enable (OE) is controlled from DSI.
2	Both output and OE are controlled from DSI.
3	Output is controlled from DSI, but OE is firmware-controlled.
4	Pin is a CSD sense pin
5	Pin is a CSD shield pin
6	Pin is connected to AMUXA
7	Pin is connected to AMUXB
8	Pin-specific Active function #0
9	Pin-specific Active function #1
10	Pin-specific Active function #2
11	Reserved
12	Pin is an LCD common pin
13	Pin is an LCD segment pin
14	Pin-specific Deep-Sleep function #0
15	Pin-specific Deep-Sleep function #1

The selection of peripheral function for different GPIO pins is given in **Table 4**.

Table 4 Port Pin Connections

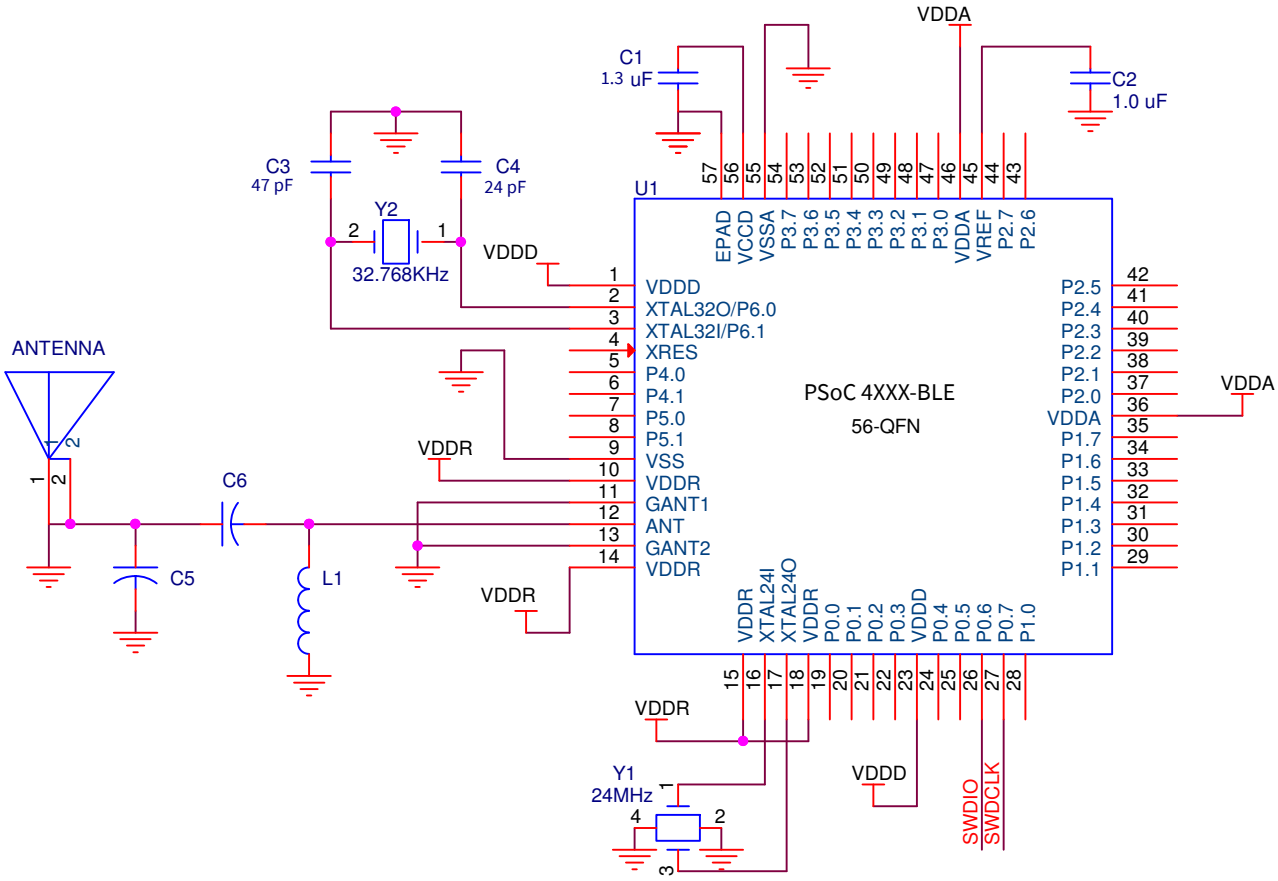
Name	Analog	Digital					
		GPIO	Active #0	Active #1	Active #2	Deep Sleep #0	Deep Sleep #1
P0.0	COMP0_INP	GPIO	TCPWM0_P[3]	SCB1_UART_RX[1]	–	SCB1_I2C_SDA[1]	SCB1_SPI_MOSI[1]
P0.1	COMP0_INN	GPIO	TCPWM0_N[3]	SCB1_UART_TX[1]	–	SCB1_I2C_SCL[1]	SCB1_SPI_MISO[1]
P0.2	–	GPIO	TCPWM1_P[3]	SCB1_UART_RTS[1]	–	COMP0_OUT[0]	SCB1_SPI_SS0[1]
P0.3	–	GPIO	TCPWM1_N[3]	SCB1_UART_CTS[1]	–	COMP1_OUT[0]	SCB1_SPI_SCLK[1]
P0.4	COMP1_INP	GPIO	TCPWM1_P[0]	SCB0_UART_RX[1]	EXT_CLK[0]/ ECO_OUT[0]	SCB0_I2C_SDA[1]	SCB0_SPI_MOSI[1]
P0.5	COMP1_INN	GPIO	TCPWM1_N[0]	SCB0_UART_TX[1]	–	SCB0_I2C_SCL[1]	SCB0_SPI_MISO[1]
P0.6	–	GPIO	TCPWM2_P[0]	SCB0_UART_RTS[1]	–	SWDIO[0]	SCB0_SPI_SS0[1]
P0.7	–	GPIO	TCPWM2_N[0]	SCB0_UART_CTS[1]	–	SWDCLK[0]	SCB0_SPI_SCLK[1]
P1.0	CTBm1_OA0_INP	GPIO	TCPWM0_P[1]	–	–	COMP0_OUT[1]	WCO_OUT[2]
P1.1	CTBm1_OA0_INN	GPIO	TCPWM0_N[1]	–	–	COMP1_OUT[1]	SCB1_SPI_SS1
P1.2	CTBm1_OA0_OUT	GPIO	TCPWM1_P[1]	–	–	–	SCB1_SPI_SS2
P1.3	CTBm1_OA1_OUT	GPIO	TCPWM1_N[1]	–	–	–	SCB1_SPI_SS3
P1.4	CTBm1_OA1_INN	GPIO	TCPWM2_P[1]	SCB0_UART_RX[0]	–	SCB0_I2C_SDA[0]	SCB0_SPI_MOSI[1]
P1.5	CTBm1_OA1_INP	GPIO	TCPWM2_N[1]	SCB0_UART_TX[0]	–	SCB0_I2C_SCL[0]	SCB0_SPI_MISO[1]
P1.6	CTBm1_OA0_INP	GPIO	TCPWM3_P[1]	SCB0_UART_RTS[0]	–	–	SCB0_SPI_SS0[1]
P1.7	CTBm1_OA1_INP	GPIO	TCPWM3_N[1]	SCB0_UART_CTS[0]	–	–	SCB0_SPI_SCLK[1]
P2.0	CTBm0_OA0_INP	GPIO	–	–	–	–	SCB0_SPI_SS1
P2.1	CTBm0_OA0_INN	GPIO	–	–	–	–	SCB0_SPI_SS2
P2.2	CTBm0_OA0_OUT	GPIO	–	–	–	WAKEUP	SCB0_SPI_SS3
P2.3	CTBm0_OA1_OUT	GPIO	–	–	–	–	WCO_OUT[1]

Table 4 Port Pin Connections *(continued)*

Name	Analog	Digital					
		GPIO	Active #0	Active #1	Active #2	Deep Sleep #0	Deep Sleep #1
P2.4	CTBm0_OA1_INN	GPIO	–	–	–	–	–
P2.5	CTBm0_OA1_INP	GPIO	–	–	–	–	–
P2.6	CTBm0_OA0_INP	GPIO	–	–	–	–	–
P2.7	CTBm0_OA1_INP	GPIO	–	–	EXT_CLK[1]/ECO_OUT[1]	–	–
P3.0	SARMUX_0	GPIO	TCPWM0_P[2]	SCB0_UART_RX[2]	–	SCB0_I2C_SDA[2]	–
P3.1	SARMUX_1	GPIO	TCPWM0_N[2]	SCB0_UART_TX[2]	–	SCB0_I2C_SCL[2]	–
P3.2	SARMUX_2	GPIO	TCPWM1_P[2]	SCB0_UART_RTS[2]	–	–	–
P3.3	SARMUX_3	GPIO	TCPWM1_N[2]	SCB0_UART_CTS[2]	–	–	–
P3.4	SARMUX_4	GPIO	TCPWM2_P[2]	SCB1_UART_RX[2]	–	SCB1_I2C_SDA[2]	–
P3.5	SARMUX_5	GPIO	TCPWM2_N[2]	SCB1_UART_TX[2]	–	SCB1_I2C_SCL[2]	–
P3.6	SARMUX_6	GPIO	TCPWM3_P[2]	SCB1_UART_RTS[2]	–	–	–
P3.7	SARMUX_7	GPIO	TCPWM3_N[2]	SCB1_UART_CTS[2]	–	–	WCO_OUT[0]
P4.0	CMOD	GPIO	TCPWM0_P[0]	SCB1_UART_RTS[0]	–	–	SCB1_SPI_MOSI[0]
P4.1	CTANK	GPIO	TCPWM0_N[0]	SCB1_UART_CTS[0]	–	–	SCB1_SPI_MISO[0]
P5.0	–	GPIO	TCPWM3_P[0]	SCB1_UART_RX[0]	EXTPA_EN	SCB1_I2C_SDA[0]	SCB1_SPI_SS0[0]
P5.1	–	GPIO	TCPWM3_N[0]	SCB1_UART_TX[0]	EXT_CLK[2]/ECO_OUT[2]	SCB1_I2C_SCL[0]	SCB1_SPI_SCLK[0]
P6.0_XTAL32O	–	GPIO	–	–	–	–	–
P6.1_XTAL32I	–	GPIO	–	–	–	–	–

The possible pin connections are shown for all analog and digital peripherals (except the radio, LCD, and CSD blocks, which were shown in **Table 1**). A typical system application connection diagram is shown in **Figure 7**.

Figure 7System Application Connection Diagram



Power

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE device can be supplied from batteries with a voltage range of 1.9 V to 5.5 V by directly connecting to the digital supply (VDDD), analog supply (VDDA), and radio supply (VDDR) pins. Internal LDOs in the device regulate the supply voltage to the required levels for different blocks. The device has one regulator for the digital circuitry and separate regulators for radio circuitry for noise isolation. Analog circuits run directly from the analog supply (VDDA) input. The device uses separate regulators for Deep Sleep and Hibernate (lowered power supply and retention) modes to minimize the power consumption. The radio stops working below 1.9 V, but the device continues to function down to 1.71 V without RF.

Bypass capacitors must be used from VDDx (x = A, D, or R) to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1-µF range in parallel with a smaller capacitor (for example, 0.1 µF). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Power Supply	Bypass Capacitors
VDDD	The internal bandgap may be bypassed with a 1-µF to 10-µF.
VDDA	0.1-µF ceramic at each pin plus bulk capacitor 1-µF to 10-µF.
VDDR	0.1-µF ceramic at each pin plus bulk capacitor 1-µF to 10-µF.
VCCD	1.3-µF ceramic capacitor at the VCCD pin.
VREF (optional)	The internal bandgap may be bypassed with a 1-µF to 10-µF capacitor.

Development Support

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE family has a rich set of documentation, development tools, and online resources to assist you during your development process. Visit **www.cypress.com/go/psoc4ble** to find out more.

Documentation

A suite of documentation supports the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE family to ensure that you can find answers to your questions quickly. This section contains a list of some of the key documents.

Software User Guide: A step-by-step guide for using PSoC Creator. The software user guide shows you how the PSoC Creator build process works in detail, how to use source control with PSoC Creator, and much more.

Component Datasheets: The flexibility of PSoC allows the creation of new peripherals (Components) long after the device has gone into production. Component datasheets provide all of the information needed to select and use a particular Component, including a functional description, API documentation, example code, and AC/DC specifications.

Application Notes: PSoC application notes discuss a particular application of PSoC in depth; examples include creating standard and custom Bluetooth LE profiles. Application notes often include example projects in addition to the application note document.

Technical Reference Manual: The Technical Reference Manual (TRM) contains all the technical detail you need to use a PSoC device, including a complete description of all PSoC registers. The TRM is available in the Documentation section at **www.cypress.com/psoc4.**

Online

In addition to print documentation, the PSoC forums connect you with fellow PSoC users and experts in PSoC from around the world, 24 hours a day, 7 days a week.

Tools

With industry standard cores, programming, and debugging interfaces, the PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE family is part of a development tool ecosystem. Visit us at **www.cypress.com/go/psoccreator** for the latest information on the revolutionary, easy to use PSoC Creator IDE, supported third party compilers, programmers, debuggers, and development kits.

Electrical Specifications

Absolute Maximum Ratings

Table 5 Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Analog, digital, or radio supply relative to V_{SS} ($V_{SSD} = V_{SSA}$)	–0.5	–	6	V	Absolute max
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute max
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD} +0.5	V	Absolute max
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	Absolute max
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for $V_{IH} > V_{DDD}$, and Min for $V_{IL} < V_{SS}$	–0.5	–	0.5	mA	Absolute max, current injected per pin
BID57	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID58	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	–
BID61	LU	Pin current for latch-up	–200	–	200	mA	–

Device-Level Specifications

All specifications are valid for –40 °C ≤ TA ≤ 85 °C and TJ ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 6 DC Specifications

Spec ID#	Parame-ter	Description	Min	Typ	Max	Units	Details/ Conditions
SID6	V_{DD}	Power supply input voltage ($V_{DDA} = V_{DDD} = V_{DD}$)	1.8	–	5.5	V	With regulator enabled
SID7	V_{DD}	Power supply input voltage unreg-ulated ($V_{DDA} = V_{DDD} = V_{DD}$)	1.71	1.8	1.89	V	Internally unregu-lated Supply
SID8	V_{DDR}	Radio supply voltage (Radio ON)	1.9	–	5.5	V	–
SID8A	V_{DDR}	Radio supply voltage (Radio OFF)	1.71	–	5.5	V	–
SID9	V_{CCD}	Digital regulator output voltage (for core logic)	–	1.8	–	V	–
SID10	C_{VCCD}	Digital regulator output bypass capacitor	1	1.3	1.6	µF	X5R ceramic or better
Active Mode, V_{DD} = 1.71 V to 5.5 V							–
SID13	I_{DD3}	Execute from flash; CPU at 3 MHz	–	2.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID14	I_{DD4}	Execute from flash; CPU at 3 MHz	–	–	–	mA	T = –40 C to 85 °C
SID15	I_{DD5}	Execute from flash; CPU at 6 MHz	–	2.5	–	mA	T = 25 °C, V_{DD} = 3.3 V

Note
1. Usage above the absolute maximum conditions listed in **Table 5** may cause permanent damage to the device.

Table 6 DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID16	I_{DD6}	Execute from flash; CPU at 6 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID17	I_{DD7}	Execute from flash; CPU at 12 MHz	–	4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID18	I_{DD8}	Execute from flash; CPU at 12 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID19	I_{DD9}	Execute from flash; CPU at 24 MHz	–	7.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID20	I_{DD10}	Execute from flash; CPU at 24 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID21	I_{DD11}	Execute from flash; CPU at 48 MHz	–	13.4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID22	I_{DD12}	Execute from flash; CPU at 48 MHz	–	–	–	mA	T = –40 °C to 85 °C
Sleep Mode, V_{DD} = 1.8 to 5.5 V							
SID23	I_{DD13}	IMO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Sleep Mode, V_{DD} and V_{DDR} = 1.9 to 5.5 V							
SID24	I_{DD14}	ECO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID25	I_{DD15}	WDT with WCO on	–	1.5	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID26	I_{DD16}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID27	I_{DD17}	WDT with WCO on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID28	I_{DD18}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID29	I_{DD19}	WDT with WCO on	–	–	–	µA	T = 25 °C
SID30	I_{DD20}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID31	I_{DD21}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID32	I_{DD22}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID33	I_{DD23}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID34	I_{DD24}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID35	I_{DD25}	Opamp on	–	–	–	µA	T = 25 °C
SID36	I_{DD26}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.8 to 3.6 V							

Table 6 DC Specifications *(continued)*

Spec ID#	Parame-ter	Description	Min	Typ	Max	Units	Details/ Conditions
SID37	I_{DD27}	GPIO and reset active	–	150	–	nA	T = 25 °C, V_{DD} = 3.3V
SID38	I_{DD28}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 3.6 to 5.5 V							
SID39	I_{DD29}	GPIO and reset active	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID40	I_{DD30}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID41	I_{DD31}	GPIO and reset active	–	–	–	nA	T = 25 °C
SID42	I_{DD32}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.8 to 3.6 V							
SID43	I_{DD33}	Stop mode current (V_{DD})	–	20	–	nA	T = 25 °C, V_{DD} = 3.3 V
SID44	I_{DD34}	Stop mode current (V_{DDR})	–	40	–-	nA	T = 25 °C, V_{DDR} = 3.3 V
SID45	I_{DD35}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID46	I_{DD36}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C, V_{DDR} = 1.9 V to 3.6 V
Stop Mode, V_{DD} = 3.6 to 5.5 V							
SID47	I_{DD37}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID48	I_{DD38}	Stop mode current (V_{DDR})	–	–	–	nA	T = 25 °C, V_{DDR} = 5 V
SID49	I_{DD39}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID50	I_{DD40}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID51	I_{DD41}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C
SID52	I_{DD42}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C

Table 7 AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	F_{CPU}	CPU frequency	DC	–	48	MHz	1.71 V ≤ V_{DD} ≤ 5.5 V
SID54	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	Guaranteed by characterization
SID55	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	–	25	µs	24-MHz IMO. Guaranteed by characterization.
SID56	$T_{HIBERNATE}$	Wakeup from Hibernate mode	–	–	0.7	ms	Guaranteed by characterization
SID57	T_{STOP}	Wakeup from Stop mode	–	–	2.2	ms	Guaranteed by characterization

GPIO

Table 8 GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID58	V_{IH}	Input voltage HIGH threshold	0.7 × V_{DD}	–	–	V	CMOS input
SID59	V_{IL}	Input voltage LOW threshold	–	–	0.3 × V_{DD}	V	CMOS input
SID60	V_{IH}	LVTTL input, V_{DD} < 2.7 V	0.7 × V_{DD}	–	-	V	–
SID61	V_{IL}	LVTTL input, V_{DD} < 2.7 V	–	–	0.3× V_{DD}	V	–
SID62	V_{IH}	LVTTL input, V_{DD} >= 2.7 V	2.0	–	-	V	–
SID63	V_{IL}	LVTTL input, V_{DD} >= 2.7 V	–	–	0.8	V	–
SID64	V_{OH}	Output voltage HIGH level	V_{DD} –0.6	–	–	V	Ioh = 4-mA at 3.3-V V_{DD}
SID65	V_{OH}	Output voltage HIGH level	V_{DD} –0.5	–	–	V	Ioh = 1-mA at 1.8-V V_{DD}
SID66	V_{OL}	Output voltage LOW level	–	–	0.6	V	Iol = 8-mA at 3.3-V V_{DD}
SID67	V_{OL}	Output voltage LOW level	–	–	0.6	V	Iol = 4-mA at 1.8-V V_{DD}
SID68	V_{OL}	Output voltage LOW level	–	–	0.4	V	Iol = 3-mA at 3.3-V V_{DD}
SID69	Rpullup	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID70	Rpulldown	Pull-down resistor	3.5	5.6	8.5	kΩ	–
SID71	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DD} = 3.3 V
SID72	I_{IL_CTBM}	Input leakage on CTBm input pins	–	–	4	nA	–
SID73	C_{IN}	Input capacitance	–	–	7	pF	–
SID74	Vhysttl	Input hysteresis LVTTL	25	40		mV	V_{DD} > 2.7 V
SID75	Vhyscmos	Input hysteresis CMOS	0.05 × V_{DD}	–	–	mV	–
SID76	Idiode	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	–
SID77	I_{TOT_GPIO}	Maximum total source or sink chip current	–	–	200	mA	–

Table 9 GPIO AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID78	T_{RISEF}	Rise time in Fast-Strong mode	2	–	12	ns	3.3-V V_{DDD}, C_{LOAD} = 25-pF
SID79	T_{FALLF}	Fall time in Fast-Strong mode	2	–	12	ns	3.3-V V_{DDD}, C_{LOAD} = 25-pF
SID80	T_{RISES}	Rise time in Slow-Strong mode	10	–	60	–	3.3-V V_{DDD}, C_{LOAD} = 25-pF
SID81	T_{FALLS}	Fall time in Slow-Strong mode	10	–	60	–	3.3-V V_{DDD}, C_{LOAD} = 25-pF

Note
2. V_{IH} must not exceed V_{DDD} + 0.2 V.

Table 9 GPIO AC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID82	$F_{GPIOUT1}$	GPIO Fout; 3.3 V ≤ V_{DD} ≤ 5.5 V. Fast-Strong mode	–	–	33	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID83	$F_{GPIOUT2}$	GPIO Fout; 1.7 V≤ V_{DD} ≤ 3.3 V. Fast-Strong mode	–	–	16.7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID84	$F_{GPIOUT3}$	GPIO Fout; 3.3 V ≤ V_{DD} ≤ 5.5 V. Slow-Strong mode	–	–	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID85	$F_{GPIOUT4}$	GPIO Fout; 1.7 V ≤ V_{DD} ≤ 3.3 V. Slow-Strong mode	–	–	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID86	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DD} ≤ 5.5 V	–	–	48	MHz	90/10% V_{IO}

Table 10 OVT GPIO DC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID71A	I_{IL}	Input leakage current (absolute value), V_{IH} > V_{DD}	–	–	10	µA	25 °C, V_{DD} = 0 V, V_{IH}= 3.0 V
SID66A	V_{OL}	Output voltage LOW level	–	–	0.4	V	I_{OL} = 20-mA, V_{DD} > 2.9-V

Table 11 OVT GPIO AC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID78A	T_{RISE_OVFS}	Output rise time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID79A	T_{FALL_OVFS}	Output fall time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID80A	T_{RISSS}	Output rise time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID81A	T_{FALLSS}	Output fall time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID82A	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DD} ≤ 5.5 V Fast-Strong mode	–	–	24	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID83A	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V ≤ V_{DD} ≤ 3.3 V Fast-Strong mode	–	–	16	MHz	90/10%, 25-pF load, 60/40 duty cycle

XRES

Table 12 XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID87	V_{IH}	Input voltage HIGH threshold	$0.7 \times V_{DDD}$	–	–	V	CMOS input
SID88	V_{IL}	Input voltage LOW threshold	–	–	$0.3 \times V_{DDD}$	V	CMOS input
SID89	Rpullup	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID90	C_{IN}	Input capacitance	–	3	–	pF	–
SID91	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	–
SID92	I_{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	–

Table 13 XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID93	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–

Analog Peripherals

Opamp

Table 14 Opamp Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
I_{DD} (Opamp Block Current. V_{DD} = 1.8 V. No Load)							
SID94	I_{DD_HI}	Power = high	–	1000	1850	µA	–
SID95	I_{DD_MED}	Power = medium	–	500	950	µA	–
SID96	I_{DD_LOW}	Power = low	–	250	350	µA	–
GBW (Load = 20 pF, 0.1 mA. V_{DDA} = 2.7 V)							
SID97	GBW_HI	Power = high	6	–	–	MHz	–
SID98	GBW_MED	Power = medium	4	–	–	MHz	–
SID99	GBW_LO	Power = low	–	1	–	MHz	–
I_{OUT_MAX} ($V_{DDA} \geq$ 2.7 V, 500 mV From Rail)							
SID100	$I_{OUT\_MAX\_HI}$	Power = high	10	–	–	mA	–
SID101	$I_{OUT\_MAX\_MID}$	Power = medium	10	–	–	mA	–
SID102	$I_{OUT\_MAX\_LO}$	Power = low	–	5	–	mA	–
I_{OUT} (V_{DDA} = 1.71 V, 500 mV From Rail)							
SID103	$I_{OUT\_MAX\_HI}$	Power = high	4	–	–	mA	–
SID104	$I_{OUT\_MAX\_MID}$	Power = medium	4	–	–	mA	–
SID105	$I_{OUT\_MAX\_LO}$	Power = low	–	2	–	mA	–
SID106	V_{IN}	Charge pump on, $V_{DDA} \geq$ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	–
SID107	V_{CM}	Charge pump on, $V_{DDA} \geq$ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	–
V_{OUT} ($V_{DDA} \geq$ 2.7 V)							
SID108	V_{OUT_1}	Power = high, I_{LOAD}=10 mA	0.5	–	V_{DDA} – 0.5	V	–
SID109	V_{OUT_2}	Power = high, I_{LOAD}=1 mA	0.2	–	V_{DDA} – 0.2	V	–
SID110	V_{OUT_3}	Power = medium, I_{LOAD}=1 mA	0.2	–	V_{DDA} – 0.2	V	–

Table 14 Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID111	V_{OUT_4}	Power = low, I_{LOAD}=0.1 mA	0.2	–	V_{DDA} – 0.2	V	–
SID112	V_{OS_TR}	Offset voltage, trimmed	1	±0.5	1	mV	High mode
SID113	V_{OS_TR}	Offset voltage, trimmed	–	±1	–	mV	Medium mode
SID114	V_{OS_TR}	Offset voltage, trimmed	–	±2	–	mV	Low mode
SID115	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/C	High mode
SID116	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Medium mode
SID117	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Low mode
SID118	CMRR	DC	70	80	–	dB	V_{DDD} = 3.6-V
SID119	PSRR	At 1 kHz, 100-mV ripple	70	85	–	dB	V_{DDD} = 3.6-V
Noise							
SID120	V_{N1}	Input referred, 1 Hz–1 GHz, power = high	–	94	–	µVrms	–
SID121	V_{N2}	Input referred, 1-kHz, power = high	–	72	–	nV/rtHz	–
SID122	V_{N3}	Input referred, 10-kHz, power = high	–	28	–	nV/rtHz	–
SID123	V_{N4}	Input referred, 100-kHz, power = high	–	15	–	nV/rtHz	–
SID124	C_{LOAD}	Stable up to maximum load. Performance specs at 50 pF	–	–	125	pF	–
SID125	Slew_rate	Cload = 50 pF, Power = High, $V_{DDA} \geq 2.7$ V	6	–	–	V/µsec	–
SID126	T_op_wake	From disable to enable, no external RC dominating	–	300	–	µsec	–
Comp_mode (Comparator Mode; 50-mV Drive, $T_{RISE} = T_{FALL}$ (Approx.)							
SID127	T_{PD1}	Response time; power = high	–	150	–	nsec	–
SID128	T_{PD2}	Response time; power = medium	–	400	–	nsec	–
SID129	T_{PD3}	Response time; power = low	–	2000	–	nsec	–
SID130	Vhyst_op	Hysteresis	–	10	–	mV	–
Deep Sleep (Deep Sleep mode operation is only guaranteed for V_{DDA} > 2.5 V)							
SID131	GBW_DS	Gain bandwidth product	–	50	–	kHz	–
SID132	IDD_DS	Current	–	15	–	µA	–
SID133	Vos_DS	Offset voltage	–	5	–	mV	–
SID134	Vos_dr_DS	Offset voltage drift	–	20	–	µV/°C	–
SID135	Vout_DS	Output voltage	0.2	–	V_{DD}–0.2	V	–
SID136	Vcm_DS	Common mode voltage	0.2	–	V_{DD}–1.8	V	–

Table 15 Comparator DC Specifications[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID140	$V_{OFFSET1}$	Input offset voltage, Factory trim	–	–	±10	mV	–
SID141	$V_{OFFSET2}$	Input offset voltage, Custom trim	–	–	±6	mV	–
SID141A	$V_{OFFSET3}$	Input offset voltage, ultra-low-power mode	–	±12	–	mV	V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID142	V_{HYST}	Hysteresis when enabled. Common Mode voltage range from 0 to VDD –1	–	10	35	mV	–
SID143	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} – 0.1	V	Modes 1 and 2
SID144	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}	V	–
SID145	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} – 1.15	V	V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID146	CMRR	Common mode rejection ratio	50	–	–	dB	V_{DDD} ≥ 2.7 V
SID147	CMRR	Common mode rejection ratio	42	–	–	dB	V_{DDD} ≤ 2.7 V
SID148	I_{CMP1}	Block current, normal mode	–	–	400	µA	–
SID149	I_{CMP2}	Block current, low power mode	–	–	100	µA	–
SID150	I_{CMP3}	Block current in ultra low-power mode	–	6	–	µA	V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C
SID151	Z_{CMP}	DC input impedance of comparator	35	–	–	MΩ	–

Table 16 Comparator AC Specifications[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID152	T_{RESP1}	Response time, normal mode, 50-mV overdrive	–	38	–	ns	50-mV overdrive
SID153	T_{RESP2}	Response time, low power mode, 50-mV overdrive	–	70	–	ns	50-mV overdrive
SID154	T_{RESP3}	Response time, ultra-low-power mode, 50-mV overdrive	–	2.3	–	µs	200-mV overdrive. V_{DDD} ≥ 2.6 V for Temp < 0°C, V_{DDD} ≥ 1.8 V for Temp > 0 °C

Note
3. ULP LCOMP operating conditions:

Temperature Sensor

Table 17 Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID155	$T_{SENSACC}$	Temperature sensor accuracy	–5	±1	5	°C	–40 to +85 °C

SAR ADC

Table 18 SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID156	A_RES	Resolution	–	–	12	bits	–
SID157	A_CHNIS_S	Number of channels - single-ended	–	–	16	–	8 full-speed
SID158	A-CHNKS_D	Number of channels - differential	–	–	8	–	Diff inputs use neighboring I/O
SID159	A-MONO	Monotonicity	–	–	–	–	Yes
SID160	A_GAINERR	Gain error	–	–	±0.1	%	With external reference.
SID161	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V V_{REF}
SID162	A_ISAR	Current consumption	–	–	1	mA	–
SID163	A_VINS	Input voltage range - single-ended	V_{SS}	–	V_{DDA}	V	–
SID164	A_VIND	Input voltage range - differential	V_{SS}	–	V_{DDA}	V	–
SID165	A_INRES	Input resistance	–	–	2.2	kΩ	–
SID166	A_INCAP	Input capacitance	–	–	10	pF	–
SID312	VREFSAR	Trimmed internal reference to SAR	–1	–	1	%	Percentage of Vbg (1.024-V)

Table 19 SAR ADC AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID167	A_psrr	Power supply rejection ratio	70	–	–	dB	Measured at 1-V reference
SID168	A_cmrr	Common mode rejection ratio	66	–	–	dB	–
SID169	A_samp	Sample rate	–	–	1	Msps	
SID313	Fsarintref	SAR operating speed without external ref. bypass	–	–	100	Ksps	12-bit resolution
SID170	A_snr	Signal-to-noise ratio (SNR)	65	–	–	dB	Fin = 10 kHz
SID171	A_bw	Input bandwidth without aliasing	–	–	A_samp/ 2	kHz	–
SID172	A_inl	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1.7	–	2	LSB	Vref = 1 V to V_{DD}
SID173	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6 V, 1 Msps	–1.5	–	1.7	LSB	Vref = 1.71 V to V_{DD}

Table 19 SAR ADC AC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID174	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1.5	–	1.7	LSB	Vref = 1 V to V_{DD}
SID175	A_dnl	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID176	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6 V, 1 Msps	–1	–	2	LSB	Vref = 1.71 V to V_{DD}
SID177	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID178	A_thd	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz

CSD

Table 20 CSD Block Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID179	V_{CSD}	Voltage range of operation	1.71	–	5.5	V	–
SID180	IDAC1	DNL for 8-bit resolution	–1	–	1	LSB	–
SID181	IDAC1	INL for 8-bit resolution	–3	–	3	LSB	–
SID182	IDAC2	DNL for 7-bit resolution	–1	–	1	LSB	–
SID183	IDAC2	INL for 7-bit resolution	–3	–	3	LSB	–
SID184	SNR	Ratio of counts of finger to noise	5	–	–	Ratio	Capacitance range of 9 to 35 pF, 0.1 pF sensitivity. Radio is not operating during the scan
SID185	I_{DAC1_CRT1}	Output current of IDAC1 (8 bits) in High range	–	612	–	µA	–
SID186	I_{DAC1_CRT2}	Output current of IDAC1 (8 bits) in Low range	–	306	–	µA	–
SID187	I_{DAC2_CRT1}	Output current of IDAC2 (7 bits) in High range	–	305	–	µA	–
SID188	I_{DAC2_CRT2}	Output current of IDAC2 (7 bits) in Low range	–	153	–	µA	–

Digital Peripherals

Timer

Table 21 Timer DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID189	I_{TIM1}	Block current consumption at 3 MHz	–	–	50	µA	16-bit timer
SID190	I_{TIM2}	Block current consumption at 12 MHz	–	–	175	µA	16-bit timer
SID191	I_{TIM3}	Block current consumption at 48 MHz	–	–	712	µA	16-bit timer

Table 22 Timer AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID192	$T_{TIMFREQ}$	Operating frequency	F_{CLK}	–	48	MHz	–
SID193	$T_{CAPWINT}$	Capture pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID194	$T_{CAPWEXT}$	Capture pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID195	T_{TIMRES}	Timer resolution	T_{CLK}	–	–	ns	–
SID196	$T_{TENWIDINT}$	Enable pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID197	$T_{TENWIDEXT}$	Enable pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID198	$T_{TIMRESWINT}$	Reset pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID199	$T_{TIMRESEXT}$	Reset pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–

Counter

Table 23 Counter DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID200	I_{CTR1}	Block current consumption at 3 MHz	–	–	50	µA	16-bit counter
SID201	I_{CTR2}	Block current consumption at 12 MHz	–	–	175	µA	16-bit counter
SID202	I_{CTR3}	Block current consumption at 48 MHz	–	–	712	µA	16-bit counter

Table 24 Counter AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID203	$T_{CTRFREQ}$	Operating frequency	F_{CLK}	–	48	MHz	–
SID204	$T_{CTRPWINT}$	Capture pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID205	$T_{CTRPWEXT}$	Capture pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID206	T_{CTRES}	Counter Resolution	T_{CLK}	–	–	ns	–
SID207	$T_{CENWIDINT}$	Enable pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID208	$T_{CENWIDEXT}$	Enable pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID209	$T_{CTRRESWINT}$	Reset pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID210	$T_{CTRRESWEXT}$	Reset pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–

Pulse Width Modulation (PWM)

Table 25 PWM DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID211	I_{PWM1}	Block current consumption at 3 MHz	–	–	50	µA	16-bit PWM
SID212	I_{PWM2}	Block current consumption at 12 MHz	–	–	175	µA	16-bit PWM
SID213	I_{PWM3}	Block current consumption at 48 MHz	–	–	741	µA	16-bit PWM

Table 26 PWM AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID214	$T_{PWMFREQ}$	Operating frequency	F_{CLK}	–	48	MHz	–
SID215	$T_{PWMPWINT}$	Pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID216	T_{PWMEXT}	Pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID217	$T_{PWMKILLINT}$	Kill pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID218	$T_{PWMKILLEXT}$	Kill pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID219	$T_{PWMEINT}$	Enable pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID220	$T_{PWMENEXT}$	Enable pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–
SID221	$T_{PWMRESWINT}$	Reset pulse width (internal)	$2 \times T_{CLK}$	–	–	ns	–
SID222	$T_{PWMRESWEXT}$	Reset pulse width (external)	$2 \times T_{CLK}$	–	–	ns	–

I^2C

Table 27 Fixed I^2C DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	I_{I2C1}	Block current consumption at 100 kHz	–	–	50	µA	–
SID224	I_{I2C2}	Block current consumption at 400 kHz	–	–	155	µA	–
SID225	I_{I2C3}	Block current consumption at 1 Mbps	–	–	390	µA	–
SID226	I_{I2C4}	I^2C enabled in Deep Sleep mode	–	–	1.4	µA	–

Table 28 Fixed I^2C AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID227	F_{I2C1}	Bit rate	–	–	1	Mbps	–

LCD Direct Drive

Table 29 LCD Direct Drive DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID228	I_{LCDLOW}	Operating current in low-power mode	–	17.5	–	µA	16 × 4 small segment display at 50 Hz
SID229	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	–
SID230	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	–
SID231	I_{LCDOP1}	LCD system operating current V_{BIAS} = 5 V.	–	2	–	mA	32 × 4 segments. 50 Hz at 25 °C
SID232	I_{LCDOP2}	LCD system operating current. V_{BIAS} = 3.3 V	–	2	–	mA	32 × 4 segments 50 Hz at 25 °C

Table 30 LCD Direct Drive AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID233	F_{LCD}	LCD frame rate	10	50	150	Hz	–

Table 31 Fixed UART DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234	I_{UART1}	Block current consumption at 100 kbps	–	–	55	µA	–
SID235	I_{UART2}	Block current consumption at 1000 kbps	–	–	360	µA	–

Table 32 Fixed UART AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID236	F_{UART}	Bit rate	–	–	1	Mbps	–

SPI Specifications

Table 33 Fixed SPI DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID237	I_{SPI1}	Block current consumption at 1 Mbps	–	–	360	µA	–
SID238	I_{SPI2}	Block current consumption at 4 Mbps	–	–	560	µA	–
SID239	I_{SPI3}	Block current consumption at 8 Mbps	–	–	600	µA	–

Table 34 Fixed SPI AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID240	F_{SPI}	SPI operating frequency (master; 6X oversampling)	–	–	8	MHz	–

Table 35 Fixed SPI Master Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID241	T_{DMO}	MOSI valid after Sclock driving edge	–	–	18	ns	–
SID242	T_{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO sampling used	20	–	–	ns	Full clock, late MISO sampling
SID243	T_{HMO}	Previous MOSI data hold time	0	–	–	ns	Referred to Slave capturing edge

Table 36 Fixed SPI Slave Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID244	T_{DMI}	MOSI valid before Sclock capturing edge	40	–	–	ns	–
SID245	T_{DSO}	MISO valid after Sclock driving edge	–	–	$42 + 3 \times T_{CPU}$	ns	–
SID246	T_{DSO_ext}	MISO valid after Sclock driving edge in external clock mode	–	–	53	ns	$V_{DD} < 3.0$ V
SID247	T_{HSO}	Previous MISO data hold time	0	–	–	ns	–
SID248	$T_{SSELSCK}$	SSEL valid to first SCK valid edge	100	–	–	ns	–

Memory

Table 37 Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID249	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–
SID309	T_{WS48}	Number of Wait states at 32–48 MHz	2	–	–		CPU execution from flash
SID310	T_{WS32}	Number of Wait states at 16–32 MHz	1	–	–		CPU execution from flash
SID311	T_{WS16}	Number of Wait states for 0–16 MHz	0	–	–		CPU execution from flash

Table 38 Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID250	$T_{ROWWRITE}$[4]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes for 128 KB flash devices Row (block) = 256 bytes for 256 KB flash devices
SID251	$T_{ROWERASE}$[4]	Row erase time	–	–	13	ms	–
SID252	$T_{ROWPROGRAM}$[4]	Row program time after erase	–	–	7	ms	–
SID253	$T_{BULKERASE}$[4]	Bulk erase time (256 KB)	–	–	35	ms	–
SID254	$T_{DEVPROG}$[4]	Total device program time	–	–	50	seconds	256 KB
SID254A			–	–	25		128 KB
SID255	F_{END}	Flash endurance	100 K	–	–	cycles	–
SID256	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	years	–
SID257	F_{RET2}	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–	years	–

Note

4. It can take as much as 20 milliseconds to write to flash. During this time, the device should not be reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin,

System Resources

Power-on-Reset (POR)

Table 39 POR DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID258	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.45	V	–
SID259	$V_{FALLIPOR}$	Falling trip voltage	0.75	–	1.40	V	–
SID260	$V_{IPORHYST}$	Hysteresis	15	–	200	mV	–

Table 40 POR AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID264	T_{PPOR_TR}	PPOR response time in Active and Sleep modes	–	–	1	µs	–

Table 41 Brown-Out Detect

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID261	$V_{FALLPPOR}$	BOD trip voltage in Active and Sleep modes	1.64	–	–	V	–
SID262	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep mode	1.4	–	–	V	–

Table 42 Hibernate Reset

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID263	$V_{HBRTRIP}$	BOD trip voltage in Hibernate mode	1.1	–	–	V	–

Voltage Monitors

Table 43 Voltage Monitor DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID265	V_{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	–
SID266	V_{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	–
SID267	V_{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	–
SID268	V_{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	–
SID269	V_{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	–
SID270	V_{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	–
SID271	V_{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	–
SID272	V_{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	–
SID273	V_{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	–
SID274	V_{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	–
SID2705	V_{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	–
SID276	V_{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	–
SID277	V_{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	–
SID278	V_{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	–
SID279	V_{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	–
SID280	V_{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	–
SID281	LVI_IDD	Block current	–	–	100	µA	–

Table 44 Voltage Monitor AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID282	$T_{MONTRIP}$	Voltage monitor trip time	–	–	1	µs	–

SWD Interface

Table 45 SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID283	F_SWDCLK1	$3.3\ V \le V_{DD} \le 5.5\ V$	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID284	F_SWDCLK2	$1.71\ V \le V_{DD} \le 3.3\ V$	–	–	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID285	T_SWDI_SETUP	T = 1/f SWDCLK	0.25 × T	–	–	ns	–
SID286	T_SWDI_HOLD	T = 1/f SWDCLK	0.25 × T	–	–	ns	–
SID287	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5 × T	ns	–
SID288	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–	ns	–

Internal Main Oscillator

Table 46 IMO DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID289	I_{IMO1}	IMO operating current at 48 MHz	–	–	1000	µA	–
SID290	I_{IMO2}	IMO operating current at 24 MHz	–	–	325	µA	–
SID291	I_{IMO3}	IMO operating current at 12 MHz	–	–	225	µA	–
SID292	I_{IMO4}	IMO operating current at 6 MHz	–	–	180	µA	–
SID293	I_{IMO5}	IMO operating current at 3 MHz	–	–	150	µA	–

Table 47 IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID296	$F_{IMOTOL3}$	Frequency variation from 3 to 48 MHz	–	–	±2	%	With API-called calibration
SID297	$F_{IMOTOL3}$	IMO startup time	–	–	12	µs	–

Internal Low-Speed Oscillator

Table 48 ILO DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID298	I_{ILO2}	ILO operating current at 32 kHz	–	0.3	1.05	µA	–

Table 49 ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID299	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID300	$F_{ILOTRIM1}$	32-kHz trimmed frequency	15	32	50	kHz	–

Table 50 External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID301	ExtClkFreq	External clock input frequency	0	–	48	MHz	CMOS input level only
SID302	ExtClkDuty	Duty cycle; Measured at $V_{DD/2}$	45	–	55	%	CMOS input level only

Table 51 UDB AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
Data Path performance							
SID303	$F_{MAX-TIMER}$	Max frequency of 16-bit timer in a UDB pair	–	–	48	MHz	–
SID304	$F_{MAX-ADDER}$	Max frequency of 16-bit adder in a UDB pair	–	–	48	MHz	–
SID305	F_{MAX_CRC}	Max frequency of 16-bit CRC/PRS in a UDB pair	–	–	48	MHz	–
PLD Performance in UDB							
SID306	F_{MAX_PLD}	Max frequency of 2-pass PLD function in a UDB pair	–	–	48	MHz	–
Clock to Output Performance							
SID307	$T_{CLK\_OUT\_UDB1}$	Prop. delay for clock in to data out at 25 °C, Typical	–	15	–	ns	–
SID308	$T_{CLK\_OUT\_UDB2}$	Prop. delay for clock in to data out, Worst case	–	25	–	ns	–

Table 52 Bluetooth LE Subsystem

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
RF Receiver Specification							
SID340	RXS, IDLE	RX sensitivity with idle transmitter	–	–89	–	dBm	–
SID340A		RX sensitivity with idle transmitter excluding Balun loss	–	–91	–	dBm	Guaranteed by design simulation
SID341	RXS, DIRTY	RX sensitivity with dirty transmitter	–	–87	–70	dBm	RF-PHY Specification (RCV-LE/CA/01/C)
SID342	RXS, HIGHGAIN	RX sensitivity in high-gain mode with idle transmitter	–	–91	–	dBm	–
SID343	PRXMAX	Maximum input power	–10	–1	–	dBm	RF-PHY Specification (RCV-LE/CA/06/C)
SID344	CI1	Co-channel interference, Wanted signal at –67 dBm and Interferer at FRX	–	9	21	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID345	CI2	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±1 MHz	–	3	15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID346	CI3	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±2 MHz	–	–29	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID347	CI4	Adjacent channel interference Wanted signal at –67 dBm and Interferer at ≥FRX ±3 MHz	–	–39	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID348	CI5	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (F_{IMAGE})	–	–20	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID349	CI6	Adjacent channel interference Wanted signal at –67 dBm and Interferer at Image frequency (F_{IMAGE} ± 1 MHz)	–	–30	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID350	OBB1	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 30–2000 MHz	–30	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID351	OBB2	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2003–2399 MHz	–35	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID352	OBB3	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2484–2997 MHz	–35	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID353	OBB4	Out-of-band blocking, Wanted signal a –67 dBm and Interferer at F = 3000–12750 MHz	–30	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID354	IMD	Intermodulation performance Wanted signal at –64 dBm and 1-Mbps Bluetooth LE, third, fourth, and fifth offset channel	–50	–	–	dBm	RF-PHY Specification (RCV-LE/CA/05/C)

Table 52 Bluetooth LE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID355	RXSE1	Receiver spurious emission 30 MHz to 1.0 GHz	–	–	–57	dBm	100-kHz measurement bandwidth ETSI EN300 328 V1.8.1
SID356	RXSE2	Receiver spurious emission 1.0 GHz to 12.75 GHz	–	–	–47	dBm	1-MHz measurement bandwidth ETSI EN300 328 V1.8.1
RF Transmitter Specifications							
SID357	TXP, ACC	RF power accuracy	–	±1	–	dB	–
SID358	TXP, RANGE	RF power control range	–	20	–	dB	–
SID359	TXP, 0dBm	Output power, 0-dB Gain setting (PA7)	–	0	–	dBm	–
SID360	TXP, MAX	Output power, maximum power setting (PA10)	–	3	–	dBm	–
SID361	TXP, MIN	Output power, minimum power setting (PA1)	–	–18	–	dBm	–
SID362	F2AVG	Average frequency deviation for 10101010 pattern	185	–	–	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID363	F1AVG	Average frequency deviation for 11110000 pattern	225	250	275	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID364	EO	Eye opening = ΔF2AVG/ΔF1AVG	0.8	–	–		RF-PHY Specification (TRM-LE/CA/05/C)
SID365	FTX, ACC	Frequency accuracy	–150	–	150	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID366	FTX, MAXDR	Maximum frequency drift	–50	–	50	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID367	FTX, INITDR	Initial frequency drift	–20	–	20	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID368	FTX, DR	Maximum drift rate	–20	–	20	kHz/ 50 µs	RF-PHY Specification (TRM-LE/CA/06/C)
SID369	IBSE1	In-band spurious emission at 2-MHz offset	–	–	–20	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID370	IBSE2	In-band spurious emission at ≥3-MHz offset	–	–	-30	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID371	TXSE1	Transmitter spurious emissions (average), <1.0 GHz	–	–	-55.5	dBm	FCC-15.247
SID372	TXSE2	Transmitter spurious emissions (average), >1.0 GHz	–	–	-41.5	dBm	FCC-15.247
RF Current Specifications							
SID373	IRX	Receive current in normal mode	–	18.7	–	mA	–
SID373A	IRX_RF	Radio receive current in normal mode	–	16.4	–	mA	Measured at V_{DDR}

Table 52 Bluetooth LE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID374	IRX, HIGHGAIN	Receive current in high-gain mode	–	21.5	–	mA	–
SID375	ITX, 3dBm	TX current at 3-dBm setting (PA10)	–	20	–	mA	–
SID376	ITX, 0dBm	TX current at 0-dBm setting (PA7)	–	16.5	–	mA	–
SID376A	ITX_RF, 0dBm	Radio TX current at 0 dBm setting (PA7)	–	15.6	–	mA	Measured at V_{DDR}
SID376B	ITX_RF, 0dBm	Radio TX current at 0 dBm excluding Balun loss	–	14.2	–	mA	Guaranteed by design simulation
SID377	ITX,-3dBm	TX current at –3-dBm setting (PA4)	–	15.5	–	mA	–
SID378	ITX,-6dBm	TX current at –6-dBm setting (PA3)	–	14.5	–	mA	–
SID379	ITX,-12dBm	TX current at –12-dBm setting (PA2)	–	13.2	–	mA	–
SID380	ITX,-18dBm	TX current at –18-dBm setting (PA1)	–	12.5	–	mA	–
SID380A	Iavg_1sec, 0dBm	Average current at 1-second Bluetooth LE connection interval	–	17.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
SID380B	Iavg_4sec, 0dBm	Average current at 4-second Bluetooth LE connection interval	–	6.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
General RF Specifications							
SID381	FREQ	RF operating frequency	2400	–	2482	MHz	–
SID382	CHBW	Channel spacing	–	2	–	MHz	–
SID383	DR	On-air data rate	–	1000	–	kbps	–
SID384	IDLE2TX	Bluetooth LE.IDLE to Bluetooth LE. TX transition time	–	120	140	µs	–
SID385	IDLE2RX	Bluetooth LE.IDLE to Bluetooth LE. RX transition time	–	75	120	µs	–
RSSI Specifications							
SID386	RSSI, ACC	RSSI accuracy	–	±5	–	dB	–
SID387	RSSI, RES	RSSI resolution	–	1	–	dB	–
SID388	RSSI, PER	RSSI sample period	–	6	–	µs	–

Table 53 ECO Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID389	F_{ECO}	Crystal frequency	–	24	–	MHz	–
SID390	F_{TOL}	Frequency tolerance	–50	–	50	ppm	–
SID391	ESR	Equivalent series resistance	–	–	60	Ω	–
SID392	PD	Drive level	–	–	100	µW	–
SID393	T_{START1}	Startup time (Fast Charge on)	–	–	850	µs	–
SID394	T_{START2}	Startup time (Fast Charge off)	–	–	3	ms	–
SID395	C_L	Load capacitance	–	8	–	pF	–
SID396	C0	Shunt capacitance	–	1.1	–	pF	–
SID397	I_{ECO}	Operating current	–	1400	–	µA	–

Table 54 WCO Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID398	F_{WCO}	Crystal frequency	–	32.768	–	kHz	–
SID399	FTOL	Frequency tolerance	–	50	–	ppm	–
SID400	ESR	Equivalent series resistance	–	50	–	kΩ	–
SID401	PD	Drive level	–	–	1	µW	–
SID402	T_{START}	Startup time	–	–	500	ms	–
SID403	C_L	Crystal load capacitance	6	–	12.5	pF	–
SID404	C0	Crystal shunt capacitance	–	1.35	–	pF	–
SID405	I_{WCO1}	Operating current (High-Power mode)	–	–	8	µA	–
SID406	I_{WCO2}	Operating current (Low-Power mode)	–	–	2.6	µA	–

Ordering Information

The PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE part numbers and features are listed in **Table 55**.

Table 55 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Part Numbers

Product Family	MPN	Max CPU Speed (MHz)	Bluetooth LE subsystem	Flash (KB)	SRAM (KB)	UDB	Opamp	CapSense	TMG (Gestures)	Direct LCD Drive	12-bit SAR ADC	DMA	LP Comparators	TCPWM Blocks	SCB Blocks	GPIO	Package	Temperature Range
PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE	CY8C4247LQI-BL473	48	4.1	128	16	4	4	–	–	–	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247FNI-BL473	48	4.1	128	16	4	4	–	–	–	1 Msps	–	2	4	2	36	CSP	85 °C
	CY8C4247LQI-BL453	48	4.1	128	16	4	4	1	–	–	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL463	48	4.1	128	16	4	4	–	–	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247FNI-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	68-CSP	85 °C
	CY8C4247FNI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	68-CSP	85 °C
	CY8C4247FNQ-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	68-CSP	105 °C
	CY8C4247LQQ-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	QFN	105 °C
	CY8C4247FLI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	Thin 68-CSP	85 °C
	CY8C4248LQI-BL473	48	4.1	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248LQI-BL453	48	4.1	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248LQI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248FLI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	Thin 76-CSP	85 °C
	CY8C4248LQI-BL543	48	4.2	256	32	–	2	–	–	–	1 Msps	1	–	4	2	36	QFN	85 °C
	CY8C4248FNI-BL543	48	4.2	256	32	–	2	–	–	–	1 Msps	1	–	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL573	48	4.2	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL573	48	4.2	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL553	48	4.2	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL553	48	4.2	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL563	48	4.2	256	32	4	4	–	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL563	48	4.2	256	32	4	4	–	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248FLI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	Thin 76-CSP	85 °C
	CY8C4248LQQ-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	105 °C
	CY8C4248FNQ-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	105 °C
	CY8C4248LQI-BL593	48	4.2	256	32	4	4	1	1	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL593	48	4.2	256	32	4	4	1	1	1	1 Msps	1	2	4	2	36	76-CSP	85 °C

PSoC 4 devices follow the part numbering convention described in the following table. All fields are single-character alphanumeric (0, 1, 2, …, 9, A,B, …, Z) unless stated otherwise.

Ordering Code Definitions

Example

CY8C 4 A B C D E F - BLXYZ

CY8 C — Cypress Prefix

4 : PSoC 4 — Architecture

2 : 4200 Family — Family within Architecture

4 : 48 MHz — Speed Grade

8 : 256 KB — Flash Capacity

LQ : QFN — Package Code

I : Industrial — Temperature Range

BLXYZ: Attributes — Attributes Code

The Field Values are listed in the following table:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family within architecture	2	PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Family
B	CPU Speed	4	48 MHz
C	Flash Capacity	8, 7	256, 128 KB respectively
DE	Package Code	FN	WLCSP
		LQ	QFN
		FL	Thin CSP
F	Temperature Range	I	Industrial
BLXYZ	Attributes Code	BL400-BL499	Bluetooth 4.1 compliant
		BL500-BL599	Bluetooth 4.2 compliant

Packaging

Table 56 Package Characteristics

Parameter	Description	Conditions	Min	Typ	Max	Units
T_A	Operating ambient temperature	–	–40	25.00	105	°C
T_J	Operating junction temperature	–	–40	–	125	°C
T_{JA}	Package θ_{JA} (56-pin QFN)	–	–	16.9	–	°C/watt
T_{JC}	Package θ_{JC} (56-pin QFN)	–	–	9.7	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball WLCSP)	–	–	20.1	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball WLCSP)	–	–	0.19	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball Thin WLCSP)	–	–	20.9	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball Thin WLCSP)	–	–	0.17	–	°C/watt
T_{JA}	Package θ_{JA} (68-ball WLCSP)		–	16.6	–	°C/watt
T_{JC}	Package θ_{JC} (68-ball WLCSP)		–	0.19	–	°C/watt
T_{JA}	Package θ_{JA} (68-ball Thin WLCSP)		–	16.6	–	°C/watt
T_{JC}	Package θ_{JC} (68-ball Thin WLCSP)		–	0.19	–	°C/watt

Table 57 Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All packages	260 °C	30 seconds

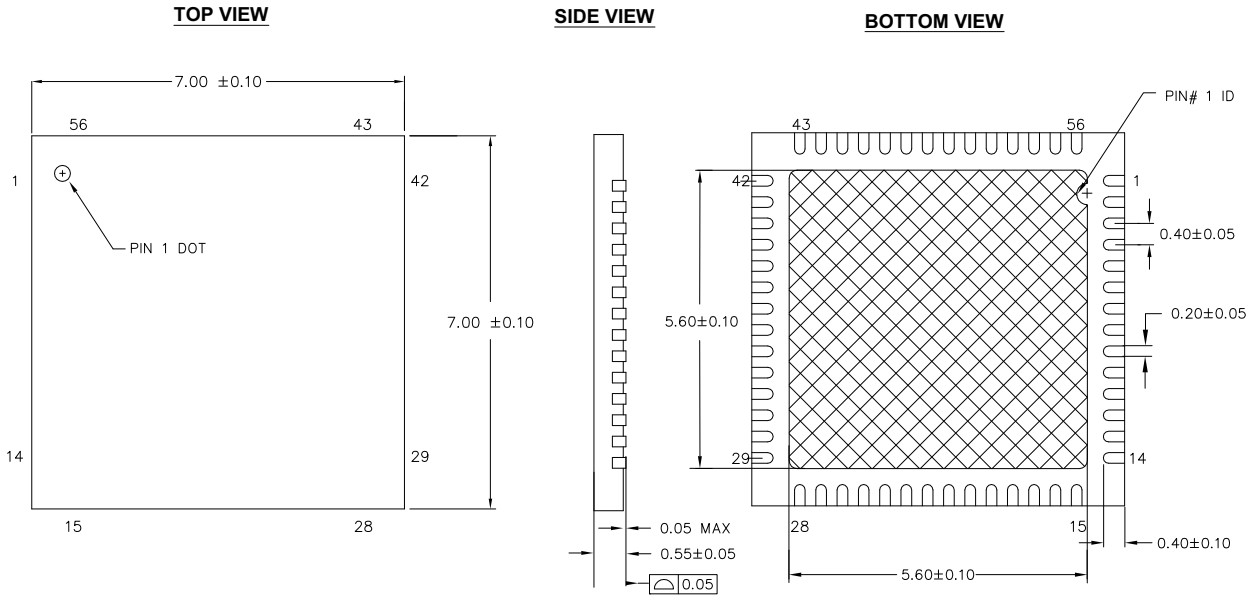
Table 58 Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
56-pin QFN	MSL 3
All WLCSP packages	MSL 1

Table 59 Package Details

Spec ID	Package	Description
001-58740 Rev. *C	56-pin QFN	7.0 mm × 7.0 mm × 0.6 mm
001-96603 Rev. *A	76-ball WLCSP	4.04 mm × 3.87 mm × 0.55 mm
002-10658, Rev. **	76-ball thin WLCSP	4.04 mm × 3.87 mm × 0.4 mm
001-92343 Rev. *A	68-ball WLCSP	3.52 mm × 3.91 mm × 0.55 mm
001-99408 Rev **	68-ball Thin WLCSP	52 mm × 3.91 mm × 0.4 mm

Figure 856-Pin QFN 7 × 7 × 0.6 mm



NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. BASED ON REF JEDEC # MO-248
3. ALL DIMENSIONS ARE IN MILLIMETERS

001-58740 *C

The center pad on the QFN package should be connected to ground (VSS) for best mechanical, thermal, and electrical performance.

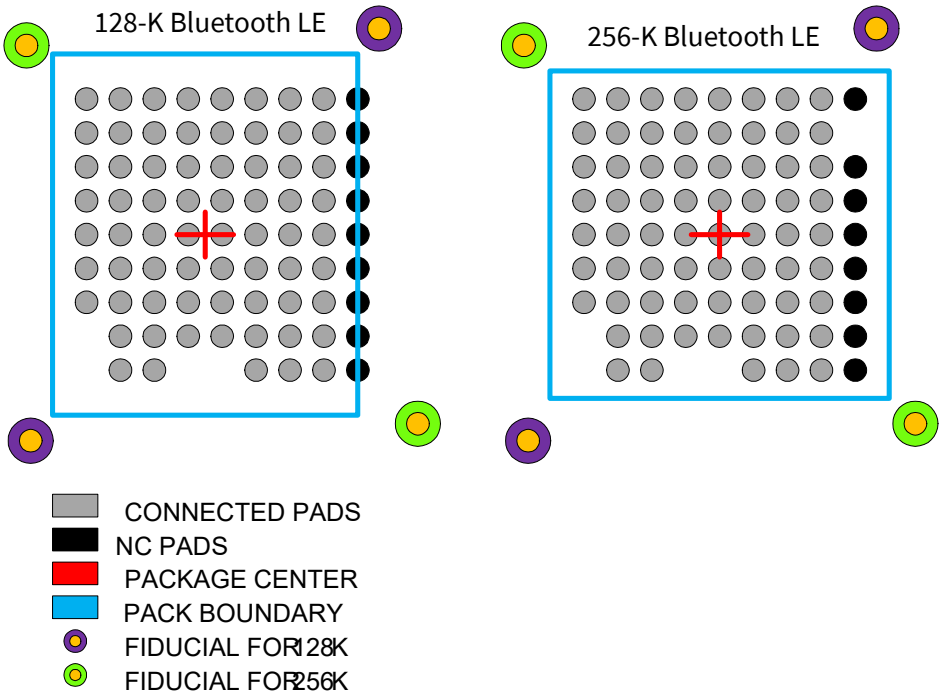
WLCSP Compatibility

The PSoC 4XXX-BLE family has products with 128 KB (16KB SRAM) and 256 KB (32KB SRAM) Flash. Package pin-outs and sizes are identical for the 56-pin QFN package but are different in one dimension for the 68-ball WLCSP.

The 256KB Flash product has an extra column of balls which are required for mechanical integrity purposes in the Chip-Scale package. With consideration for this difference, the land pattern on the PCB may be designed such that either product may be used with no change to the PCB design.

Figure 9 shows the 128KB and 256 KB Flash CSP packages.

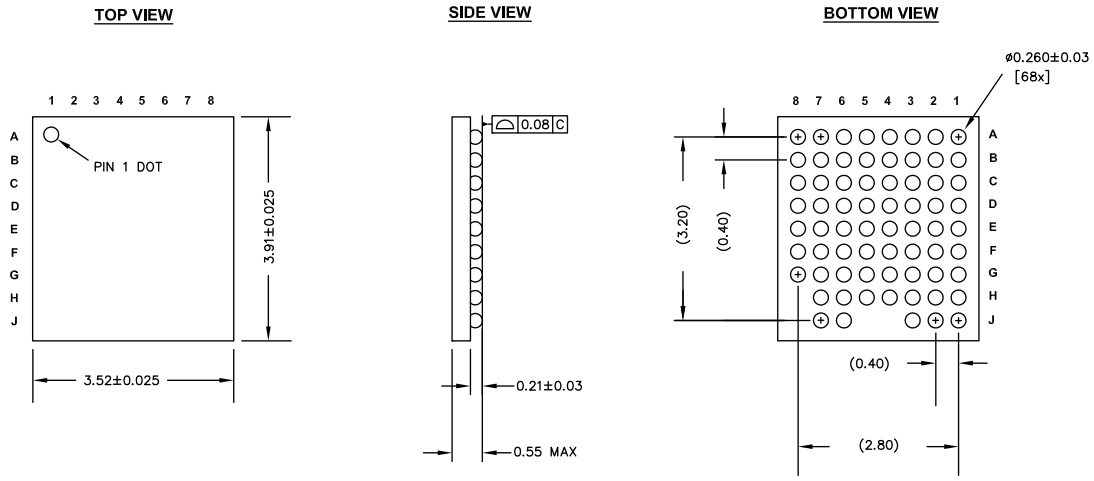
Figure 9128KB and 256 KB Flash CSP Packages



The rightmost column of (all NC, No Connect) balls in the 256K Bluetooth LE WLCSP is for mechanical integrity purposes. The package is thus wider (3.2 mm versus 2.8 mm). All other dimensions are identical. Infineon will provide layout symbols for PCB layout.

The scheme in **Figure 9** is implemented to design the PCB for the 256K Bluetooth LE package with the appropriate space requirements thus allowing use of either package at a later time without redesigning the Printed Circuit Board.

Figure 1068-Ball WLCSP Package Outline

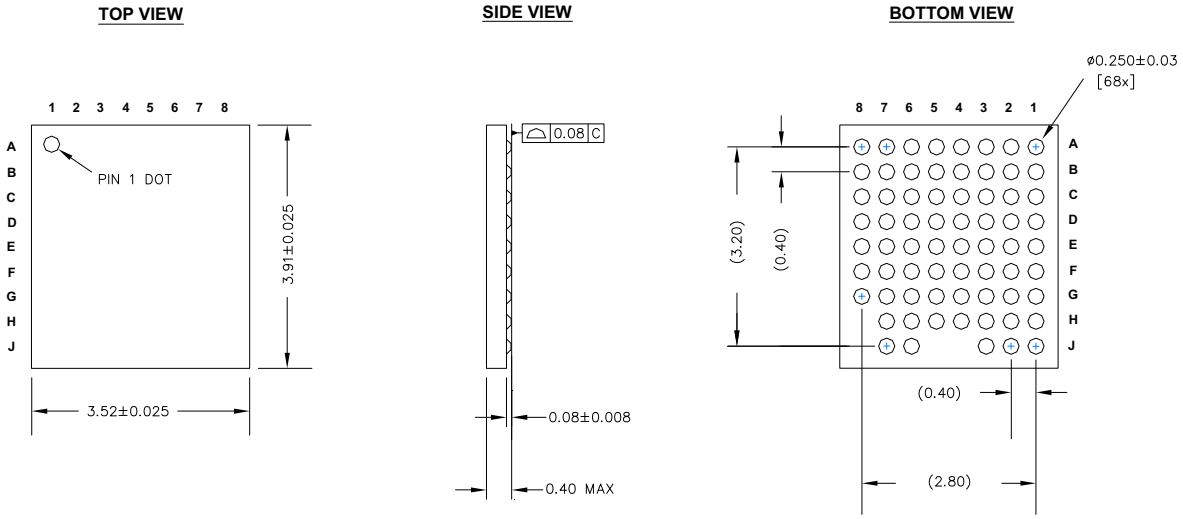


NOTES:

1. REFERENCE JEDEC PUBLICATION 95, DESIGN GUIDE 4.18
2. ALL DIMENSIONS ARE IN MILLIMETERS

001-92343 *A

Figure 1168-Ball Thin WLCSP

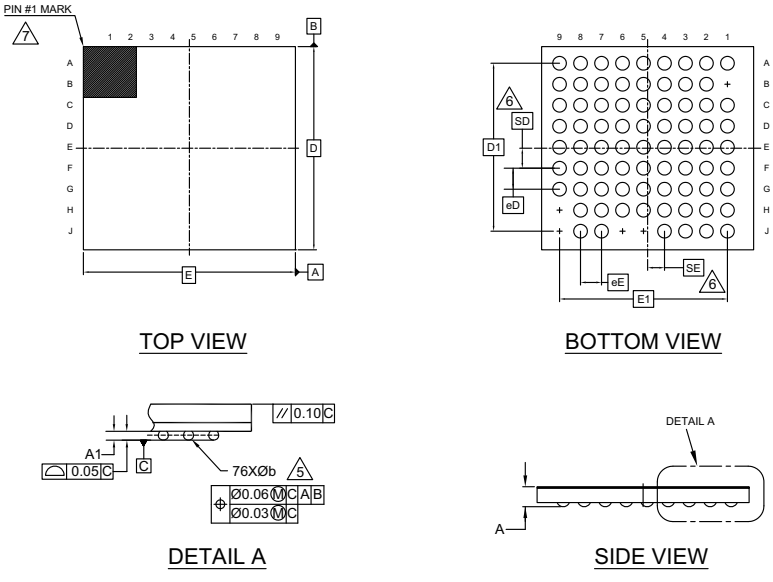


NOTES:

1. REFERENCE JEDEC PUBLICATION 95, DESIGN GUIDE 4.18
2. ALL DIMENSIONS ARE IN MILLIMETERS

001-99408 **

Figure 1276-Ball WLCSP Package Outline



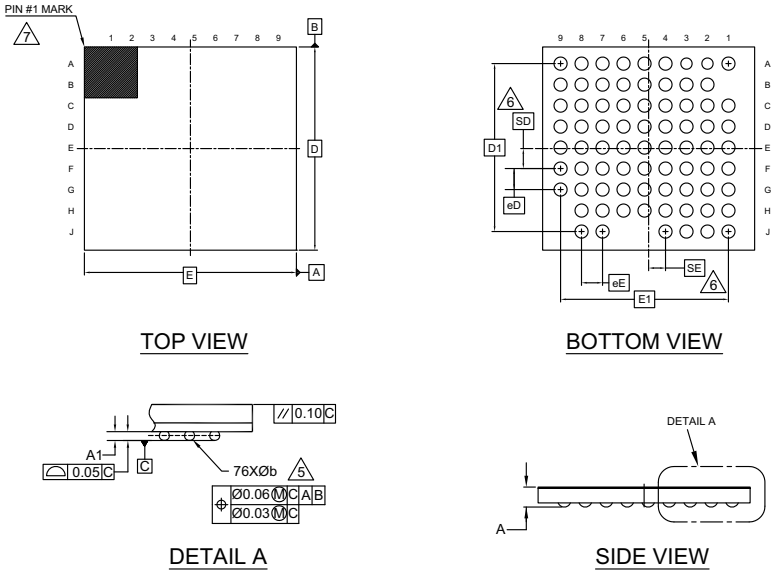
SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	0.55
A1	0.18	0.21	0.24
D	3.87 BSC		
E	4.04 BSC		
D1	3.20 BSC		
E1	3.20 BSC		
MD	9		
ME	9		
N	76		
Ø b	0.23	0.26	0.29
eD	0.40 BSC		
eE	0.40 BSC		
SD	0.381 BSC		
SE	0.321 BSC		

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.
9. JEDEC SPECIFICATION NO. REF : N/A

001-96603 *B

Figure 1376-Ball Thin WLCSP Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	0.40
A1	0.072	0.08	0.088
D	3.87 BSC		
E	4.04 BSC		
D1	3.20 BSC		
E1	3.20 BSC		
MD	9		
ME	9		
N	76		
Ø b	0.22	0.25	0.28
eD	0.40 BSC		
eE	0.40 BSC		
SD	0.381		
SE	0.321		

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.

002-10658 **

Acronyms

Table 60 Acronyms Used in this Document

Acronym	Description	Acronym	Description
ABUS	analog local bus	EEPROM	electrically erasable programmable read-only memory
ADC	analog-to-digital converter	EMI	electromagnetic interference
AG	analog global	EMIF	external memory interface
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an Arm data transfer bus	EOC	end of conversion
ALU	arithmetic logic unit	EOF	end of frame
AMUXBUS	analog multiplexer bus	EPSR	execution program status register
API	application programming interface	ESD	electrostatic discharge
APSR	application program status register	ETM	embedded trace macrocell
Arm®	advanced RISC machine, a CPU architecture	FET	field-effect transistor
ATM	automatic thump mode	FIR	finite impulse response, see also IIR
BW	bandwidth	FPB	flash patch and breakpoint
CAN	Controller Area Network, a communications protocol	FS	full-speed
CMRR	common-mode rejection ratio	GPIO	general-purpose input/output, applies to a PSoC pin
CPU	central processing unit	HCI	host controller interface
CRC	cyclic redundancy check, an error-checking protocol	HVI	high-voltage interrupt, see also LVI, LVD
DAC	digital-to-analog converter, see also IDAC, VDAC	IC	integrated circuit
DFB	digital filter block	IDAC	current DAC, see also DAC, VDAC
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.	IDE	integrated development environment
DMIPS	Dhrystone million instructions per second	I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
DMA	direct memory access, see also TD	IIR	infinite impulse response, see also FIR
DNL	differential nonlinearity, see also INL	ILO	internal low-speed oscillator, see also IMO
DNU	do not use	IMO	internal main oscillator, see also ILO
DR	port write data registers	INL	integral nonlinearity, see also DNL
DSI	digital system interconnect	I/O	input/output, see also GPIO, DIO, SIO, USBIO
DWT	data watchpoint and trace	IPOR	initial power-on reset
ECC	error correcting code	IPSR	interrupt program status register
ECO	external crystal oscillator	IRQ	interrupt request

Table 60 Acronyms Used in this Document *(continued)*

Acronym	Description	Acronym	Description
ITM	instrumentation trace macrocell	PSRR	power supply rejection ratio
LCD	liquid crystal display	PWM	pulse-width modulator
LIN	Local Interconnect Network, a communications protocol.	RAM	random-access memory
LR	link register	RISC	reduced-instruction-set computing
LUT	lookup table	RMS	root-mean-square
LVD	low-voltage detect, see also LVI	RTC	real-time clock
LVI	low-voltage interrupt, see also HVI	RTL	register transfer language
LVTTL	low-voltage transistor-transistor logic	RTR	remote transmission request
MAC	multiply-accumulate	RX	receive
MCU	microcontroller unit	SAR	successive approximation register
MISO	master-in slave-out	SC/CT	switched capacitor/continuous time
NC	no connect	SCL	I^2C serial clock
NMI	nonmaskable interrupt	SDA	I^2C serial data
NRZ	non-return-to-zero	S/H	sample and hold
NVIC	nested vectored interrupt controller	SINAD	signal to noise and distortion ratio
NVL	nonvolatile latch, see also WOL	SIO	special input/output, GPIO with advanced features. See GPIO.
Opamp	operational amplifier	SOC	start of conversion
PAL	programmable array logic, see also PLD	SOF	start of frame
PC	program counter	SPI	Serial Peripheral Interface, a communications protocol
PCB	printed circuit board	SR	slew rate
PGA	programmable gain amplifier	SRAM	static random access memory
PHUB	peripheral hub	SRES	software reset
PHY	physical layer	STN	super twisted nematic
PICU	port interrupt control unit	SWD	serial wire debug, a test protocol
PLA	programmable logic array	SWV	single-wire viewer
PLD	programmable logic device, see also PAL	TD	transaction descriptor, see also DMA
PLL	phase-locked loop	THD	total harmonic distortion
PMDD	package material declaration data sheet	TIA	transimpedance amplifier
POR	power-on reset	TN	twisted nematic
PRES	precise power-on reset	TRM	technical reference manual
PRS	pseudo random sequence	TTL	transistor-transistor logic
PS	port read data register	TX	transmit
PSoC™	Programmable System-on-Chip™	UART	Universal Asynchronous Transmitter Receiver, a communications protocol

Table 60 Acronyms Used in this Document *(continued)*

Acronym	Description	Acronym	Description
UDB	universal digital block	WOL	write once latch, see also NVL
USB	Universal Serial Bus	WRES	watchdog timer reset
USBIO	USB input/output, PSoC pins used to connect to a USB port	XRES	external reset I/O pin
VDAC	voltage DAC, see also DAC, IDAC	XTAL	crystal
WDT	watchdog timer		

Document Conventions

Units of Measure

Table 61 Units of Measure

Symbol	Unit of Measure	Symbol	Unit of Measure
°C	degrees Celsius	µH	microhenry
dB	decibel	µs	microsecond
dBm	decibel-milliwatts	µV	microvolt
fF	femtofarads	µW	microwatt
Hz	hertz	mA	milliampere
KB	1024 bytes	ms	millisecond
kbps	kilobits per second	mV	millivolt
Khr	kilohour	nA	nanoampere
kHz	kilohertz	ns	nanosecond
kΩ	kilo ohm	nV	nanovolt
ksps	kilosamples per second	Ω	ohm
LSB	least significant bit	pF	picofarad
Mbps	megabits per second	ppm	parts per million
MHz	megahertz	ps	picosecond
MΩ	mega-ohm	s	second
Msps	megasamples per second	sps	samples per second
µA	microampere	sqrtHz	square root of hertz
µF	microfarad	V	volt

Revision History

Description Title: PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Family Datasheet Programmable System-on-Chip Document Number: 002-23053			
Revision	**ECN**	**Submission Date**	**Description of Change**
**	6078076	02/22/2018	New datasheet
*A	7161218	06/16/2021	Updated datasheet to IFX template. Changed title to “PSoC™ 4 CY8C42xx-BL MCU with AIROC™ Bluetooth® LE Family Datasheet” Replaced BLE to Bluetooth LE.

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